Nuclear Instruments and Methods in Physics Research B59/60 (1991) 1477–1502
North-Holland

Author index

Abe, Y., see Sato, S. . . . B59/60 (1991) 1391
Abonneau, E., A. Perez, G. Fuchs and M. Treilleux, Microstructural and chemical characterization of ion beam mixed Fe/Al_2O_3 interface; effect on adhesion enhancement . . . B59/60 (1991) 1183
Abraham, M.M., see Chen, Y. . . . B59/60 (1991) 1163
Adachi, M., S. Ikuni, K. Yamada, H. Usui and I. Yamada, Optical characteristics of high-power excimer laser mirrors of single-crystal aluminum film with high reflectance and durability . . . B59/60 (1991) 940
Adams, P.M., see Knudsen, J.F. . . . B59/60 (1991) 1067
Adesida, I., see Guggina, W.H. . . . B59/60 (1991) 1011
Akasaka, Y., see Tsukamoto, K. . . . B59/60 (1991) 584
Akiba, H., see Suzuki, Y. . . . B59/60 (1991) 698
Al-Bayati, A.H., see Orrman-Rossiter, K.G. . . . B59/60 (1991) 197
Albridge, R.G., see Wang, P.W. . . . B59/60 (1991) 1317
Alexander, D.E., G.S. Was and L.E. Rehn, Ion-induced grain growth in multilayer and coevaporated metal alloy thin films . . . B59/60 (1991) 462
Alford, T.L., B. Blanpain, L.H. Allen and J.W. Mayer, In-situ resistance measurements during ion-induced Pt/Al amorphous phase formation . . . B59/60 (1991) 401
Alkaisi, M.H., see Auner, G.W. . . . B59/60 (1991) 504
Alkaisi, M.H., see Cheng, Y.-T. . . . B59/60 (1991) 509
Allen, L.H., see Alford, T.L. . . . B59/60 (1991) 401
Allen, W.R. and D.F. Pedraza, High-energy iron ion implantation into sapphire . . . B59/60 (1991) 1159
Almuratov, R.U., see Lifanova, L.F. . . . B59/60 (1991) 241
Alves, E., see Feuser, U. . . . B59/60 (1991) 1049
Alves, E., see Soares, J.C. . . . B59/60 (1991) 1090
Amaral, L., see Kaschny, J.R. . . . B59/60 (1991) 1281
Ameen, M.S., see Soble II, C.N. . . . B59/60 (1991) 155
Ando, T., see Tamura, M. . . . B59/60 (1991) 572
Andoh, Y., see Ogata, K. . . . B59/60 (1991) 225
Andoh, Y., see Ogata, K. . . . B59/60 (1991) 229
Andoh, Y., S. Nishiyama, H. Kirimura, T. Mikami, K. Ogata and F. Fujimoto, The effect of adding gas ions to a beam for deposition of boron nitride films by the ion beam and vapor deposition method . . . B59/60 (1991) 276
Andoh, Y., see Sakai, S. . . . B59/60 (1991) 288
Andoh, Y., see Miyano, T. . . . B59/60 (1991) 1167
Andrews, J.W., see Hu, Y.Z. . . . B59/60 (1991) 76
Anjum, M., see Sandhu, G.S. . . . B59/60 (1991) 145
Antolak, A.J., B.N. Handy, D.H. Morse and A.E. Pontau, Energy loss and straggling measurements of ions in solid absorbers . . . B59/60 (1991) 13
Armour, D.G., see Orrman-Rossiter, K.G. . . . B59/60 (1991) 197
Armour, D.G., see Gordon, J.S. . . . B59/60 (1991) 312
Arnold, A., R. Ramlau and E.H. te Kaat, Cross-sectional TEM investigations of iron after high-dose nitrogen implantation . . . B59/60 (1991) 726
Arnold, G.W., see Polman, A. . . . B59/60 (1991) 1313
Arora, B.M., see Salvi, V.P. . . . B59/60 (1991) 1124
Arsubov, N.M., see Ryabchikov, A.I. . . . B59/60 (1991) 124
Asari, M., see Kobayashi, N. . . . B59/60 (1991) 449
Atwater, H.A., J.S. Im and W.L. Brown, Heterogeneous amorphization of Si during ion irradiation: dependence of amorphous Si nucleation kinetics on defect energy and structure . . . B59/60 (1991) 386
Atwater, H.A., see Im, J.S. . . . B59/60 (1991) 422
Auciello, O., see Soble II, C.N. . . . B59/60 (1991) 155
Audet, S.A., see White, A.E. . . . B59/60 (1991) 693
Audouard, A., E. Balanzat, S. Bouffard, J.C. Jousset, A. Chamberod, A. Dunlop, D. Lesueur, G. Fuchs, R. Spohr, J. Vetter and L. Thomé, Structural modifications of crystalline and amorphous Ni_3B irradiated with high-energy heavy ions . . . B59/60 (1991) 414

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Auner, G.W., Y.-T. Cheng, M.H. Alkaisi, M.M. Karmarkar and K.R. Padmanabhan, Cohesive energy effects on anisotropic transport in ion mixing . . . B59/60 (1991) 504
Auner, G.W., see Cheng, Y.-T. . . . B59/60 (1991) 509
Averback, R.S., see Hsieh, H. . . . B59/60 (1991) 203
Averback, R.S., T. Diaz de la Rubia, H. Hsieh and R. Benedek, Interactions of energetic particles and clusters with solids . . . B59/60 (1991) 709

Babsail, L., N. Hamelin and P.D. Townsend, Helium-ion implanted waveguides in zircon . . . B59/60 (1991) 1219
Baglin, J.E.E., see Kellock, A.J. . . . B59/60 (1991) 249
Balanzat, E., see Audouard, A. . . . B59/60 (1991) 414
Baldo, P.M., see Woo, J.J. . . . B59/60 (1991) 537
Baldo, P.M., see Rehn, L.E. . . . B59/60 (1991) 1463
Ballegeer, D.G., see Guggina, W.H. . . . B59/60 (1991) 1011
Bao, J.R., see Lin, S.H. . . . B59/60 (1991) 1257
Bao, Z.X., see Saleh, A.A. . . . B59/60 (1991) 1372
Barbour, J.C., E.L. Venturini and D.S. Ginley, Irradiation-induced pinning in single-crystal and thin-film $Tl_2Ca_2Ba_2Cu_3O_y$ superconductors . . . B59/60 (1991) 1395
Bardin, T.T., see Kellock, A.J. . . . B59/60 (1991) 249
Bardin, T.T., see Tin, C.C. . . . B59/60 (1991) 623
Barnes, P.A., see Tin, C.C. . . . B59/60 (1991) 623
Barth, M., W. Ensinger, V. Hoffmann and G.K. Wolf, Stress and adhesion of chromium and boron films deposited under ion bombardment . . . B59/60 (1991) 254
Barth, M., see Liu Xianghuai . . . B59/60 (1991) 851
Basu, S.N., see Bordes, N. . . . B59/60 (1991) 1399
Battaglia, A., F. Priolo and E. Rimini, Influence of doping on ion-induced growth and shrinkage of partial damage in silicon . . . B59/60 (1991) 382
Baur, M., see Kallweit, R. . . . B59/60 (1991) 1288
Becker, K., L. Yang, R.F. Haglund Jr, R.H. Magruder, R.A. Weeks and R.A. Zuhr, Laser-induced fluorescence and nonlinear optical properties of ion-implanted fused silica . . . B59/60 (1991) 1304
Bedell, C.J., H.E. Bishop, G. Dearnaley, J.E. Desport, H. Romary and J-M. Romary, Oxidation-resistant coatings on titanium alloys by ion beam assisted deposition . . . B59/60 (1991) 245
Behar, M., P.L. Grande, R. Wagner de Oliveira and J.P. Biersack, Range parameters of heavy ions implanted into boron films . . . B59/60 (1991) 1
Behar, M., see Kaschny, J.R. . . . B59/60 (1991) 1281
Bello, I., see Lau, W.M. . . . B59/60 (1991) 316
Belykh, S.F., I.V. Redina and V.Kh. Ferleger, Excited-state formation model for metal-oxide sputtered molecules B59/60 (1991) 65
Belykh, S.F., R.N. Evtukhov, I.V. Redina and V.Kh. Ferleger, Sputter-induced photon emission study at various doses of implanted ions . . . B59/60 (1991) 72
Belykh, S.F., R.N. Evtukhov, U.Kh. Rasulev and I.V. Redina, Application of luminous ion beams in direct ion optical characteristics measurements . . . B59/60 (1991) 106
Bench, M.W., I.M. Robertson and M.A. Kirk, Transmission electron microscopy investigation of the damage produced in individual displacement cascades in GaAs and GaP . . . B59/60 (1991) 372
Bench, M.W., see Jenčič, I. . . . B59/60 (1991) 458
Benedek, R., see Averback, R.S. . . . B59/60 (1991) 709
Beng, R.Z., see Zhu, J.L. . . . B59/60 (1991) 1045
Benit, J., W.L. Brown and C.G. Maclennan, Computer simulation of sputtering of oxygen and water molecules from thin films of water ice . . . B59/60 (1991) 68
Benyagoub, A., L. Thomé, J. Fontenille and E. Ligeon, Ion beam modification of amorphous clusters formed in ion-implanted Ni–P alloys . . . B59/60 (1991) 418
Berg, S., see Biersack, J.P. . . . B59/60 (1991) 21
Bhattacharya, R.S., see Rai, A.K. . . . B59/60 (1991) 280
Bhattacharya, R.S., A.K. Rai and A. Erdemir, High energy (MeV) ion beam modifications of sputtered MoS_2 coatings on sapphire . . . B59/60 (1991) 788
Bhattacharya, R.S., R.L.C. Wu and C.S. Yust, Tribological properties of ion beam deposited diamond-like carbon film on silicon nitride . . . B59/60 (1991) 1383
Biersack, J.P., see Behar, M. . . . B59/60 (1991) 1
Biersack, J.P., S. Berg and C. Nender, T-DYN Monte Carlo simulations applied to ion assisted thin film processes B59/60 (1991) 21
Birtcher, R.C. and L.M. Wang, Microstructural changes induced in Zr_3Al and U_3Si during irradiation of the crystalline state . . . B59/60 (1991) 966
Bishop, H.E., see Bedell, C.J. . . . B59/60 (1991) 245
Blanpain, B., see Alford, T.L. . . . B59/60 (1991) 401
Bodart, F., see Terwagne, G. . . . B59/60 (1991) 93

Bodart, F., see Lucas, S. . . . B59/60 (1991) 925
Bond, P., see Ridgway, M.C. . . . B59/60 (1991) 164
Bonnett, J.D., see Howe, L.M. . . . B59/60 (1991) 884
Bordes, N., S.N. Basu, A.D. Rollett and M. Nastasi, Properties of thin-film $YBa_2Cu_3O_{7-x}$ superconductors grown on ion-irradiated $SrTiO_3$ substrates . . . B59/60 (1991) 1399
Børgesen, P., D.A. Lilienfeld and H. Msaad, Low-temperature ion beam mixing of medium-Z metals . . . B59/60 (1991) 563
Bouffard, S., see Audouard, A. . . . B59/60 (1991) 414
Bourcier, R.J., D.M. Follstaedt, M.T. Dugger and S.M. Myers, Mechanical characterization of several ion-implanted alloys: nanoindentation testing, wear testing and finite element modeling . . . B59/60 (1991) 905
Bourcier, R.J., see Follstaedt, D.M. . . . B59/60 (1991) 909
Bourgault, D., see Costantini, J.M. . . . B59/60 (1991) 600
Brand, R.A., see Tosello, C. . . . B59/60 (1991) 545
Brasure, L.W., see Prinja, A.K. . . . B59/60 (1991) 46
Braun, M., Reduced wear and cladding performances of several materials by nitrogen ion implantation . . . B59/60 (1991) 914
Braunstein, G., see Lee, S.-T. . . . B59/60 (1991) 999
Braunstein, G., S. Chen, S.-T. Lee, L.R. Zheng, K.Y. Ko, D.L. Peterson and D. Lawrence, Compensation phenomena in GaAs implanted with 1 MeV silicon ions . . . B59/60 (1991) 1032
Brebner, J.L., see Trudeau, Y.B. . . . B59/60 (1991) 609
Brenier, R., see Romana, L. . . . B59/60 (1991) 567
Bridwell, L.B., R.E. Giedd, Wang Yongqiang, S.S. Mohite, T. Jahnke and I.M. Brown, Electrical conductivity enhancement of polyethersulfone (PES) by ion implantation . . . B59/60 (1991) 1240
Brijs, G., see Maex, K. . . . B59/60 (1991) 660
Brisard, F., see Costantini, J.M. . . . B59/60 (1991) 600
Brown, D.W., Z.A. Munir and R.G. Musket, A precipitate coarsening mechanism for buried layer formation by ion implantation . . . B59/60 (1991) 627
Brown, I.G., see Hou, P.Y. . . . B59/60 (1991) 1345
Brown, I.M., see Bridwell, L.B. . . . B59/60 (1991) 1240
Brown, R., see Cowie, J.G. . . . B59/60 (1991) 871
Brown, W.L., see Benit, J. . . . B59/60 (1991) 68
Brown, W.L., M.F. Jarrold, R.L. McEachern, M. Sosnowski, G. Takaoka, H. Usui and I. Yamada, Ion cluster beam deposition of thin films . . . B59/60 (1991) 182
Brown, W.L., see Atwater, H.A. . . . B59/60 (1991) 386
Brunel, M., see Romana, L. . . . B59/60 (1991) 567
Brunel, M., see Ramos, S.M.M. . . . B59/60 (1991) 1201
Brunel, M., see Donnet, C. . . . B59/60 (1991) 1205
Bruynseraede, Y., see Vantomme, A. . . . B59/60 (1991) 680
Buchal, Ch., Ion beam modification of electro-optical crystals . . . B59/60 (1991) 1142
Buchal, Ch., see Niehof, A. . . . B59/60 (1991) 1355
Buchanan, R.A., see Williams, J.M. . . . B59/60 (1991) 845
Budinov, H., see Vitali, G. . . . B59/60 (1991) 1077
Budinov, H.I. and D.S. Karpuzov, Defect depth profiles in B^+ and As^+ implanted Si . . . B59/60 (1991) 1041
Bultena, S., see Touhouche, K. . . . B59/60 (1991) 676
Buravlev, A.V., see Vyatkin, A.F. . . . B59/60 (1991) 431
Burkhalter, P.G., see Hubler, G.K. . . . B59/60 (1991) 268
Burns, F.C., see Williams, J.M. . . . B59/60 (1991) 845
Burte, E.P., see Ye, M. . . . B59/60 (1991) 528
Burton, L.C., see Vaseashta, A. . . . B59/60 (1991) 1023
Buters, W.Th.M., see Hoondert, W.H.B. . . . B59/60 (1991) 1340
Butz, R., see Li, J. . . . B59/60 (1991) 989
Butz, R., see Holländer, B. . . . B59/60 (1991) 994
Byers, P., see Ridgway, M.C. . . . B59/60 (1991) 164

Calcagno, L. and G. Foti, Ion irradiation of polymers . . . B59/60 (1991) 1153
Campisano, S.U., see Spinella, C. . . . B59/60 (1991) 363
Canut, B., see Romana, L. . . . B59/60 (1991) 567
Canut, B., see Ramos, S.M.M. . . . B59/60 (1991) 1201
Canut, B., J.P. Dupin, L. Gea, S.M.M. Ramos and P. Thevenard, Anomalous diffusion effects in ion implanted MgO single crystals . . . B59/60 (1991) 1211
Caro, J.A. and D.F. Pedraza, The stability of irradiation-induced defects in NiAl . . . B59/60 (1991) 880
Carosella, C.A., see Hubler, G.K. . . . B59/60 (1991) 268
Carter, C.B., see Norton, M. G. . . . B59/60 (1991) 1215

Cavasin, D. and G.S. Was, Experimental determination of transformation enthalpies of metastable phase transitions in ion-irradiated $NiAl_3$ . . . B59/60 (1991) 875
Cerny, F., M. Prazak and J. Suchanek, Electrochemical and mechanical properties of alloy steels implanted by nitrogen ions . . . B59/60 (1991) 762
Chakrabarti, U.K., see Pearton, S.J. . . . B59/60 (1991) 1015
Chamberod, A., see Audouard, A. . . . B59/60 (1991) 414
Chandler, P.J., see Zhang, L. . . . B59/60 (1991) 1147
Chandler, P.J., L. Zhang and P.D. Townsend, Ion implanted waveguides in laser host materials . . . B59/60 (1991) 1223
Chaudhari, S.M., see Ogale, S.B. . . . B59/60 (1991) 1350
Chayahara, A., see Horino, Y. . . . B59/60 (1991) 139
Chayahara, A., see Ensinger, W. . . . B59/60 (1991) 259
Chayahara, A., see Sanda, H. . . . B59/60 (1991) 778
Chayahara, A., see Lu, Y.F. . . . B59/60 (1991) 861
Chayahara, A., S. Nakashima, M. Hashimoto, T. Sasaki, M. Kurokawa, S. Kiyama and M. Satou, Martensitic transformation of type 304 stainless steel by high-energy ion implantation . . . B59/60 (1991) 893
Chayahara, A., see Yokota, K. . . . B59/60 (1991) 1431
Chechenin, N., see Sarholt-Kristensen, L. . . . B59/60 (1991) 85
Chen, A., see Qiu, X. . . . B59/60 (1991) 951
Chen, L.J., see Chu, C.H. . . . B59/60 (1991) 391
Chen, L.J., see Hsu, S.N. . . . B59/60 (1991) 1037
Chen, L.Z., see Xu, X.L. . . . B59/60 (1991) 1267
Chen, S., see Lee, S.-T. . . . B59/60 (1991) 999
Chen, S., see Braunstein, G. . . . B59/60 (1991) 1032
Chen, W.S., see Huang, F.S. . . . B59/60 (1991) 1003
Chen, Y., M.M. Abraham and D.F. Pedraza, Radiation damage in Al_2O_3 crystals implanted with 3.8 MeV Fe^{2+} ions . . . B59/60 (1991) 1163
Cheng, Y.-T., see Auner, G.W. . . . B59/60 (1991) 504
Cheng, Y.-T., G.W. Auner, M.H. Alkaisi, K.R. Padmanabhan and M.M. Karmarkar, Thermodynamic and ballistic aspects of ion mixing . . . B59/60 (1991) 509
Chen Jun, see Zhang Tonghe . . . B59/60 (1991) 828
Chen Youshan, see Wang Xi . . . B59/60 (1991) 272
Chen Yuanru, Li Shizhuo, Zhang Xushou, Liu Hong, Yang Genqing and Qu Baochun, Mechanical and tribological properties of silicon nitride films synthesized by ion beam enhanced deposition . . . B59/60 (1991) 1295
Cherekdjian, S., see Sandhu, G.S. . . . B59/60 (1991) 145
Chernysh, V.S., see Sarholt-Kristensen, L. . . . B59/60 (1991) 85
Chivers, D.J., see Ridgway, M.C. . . . B59/60 (1991) 164
Cho, S.J., H.S. Choe, S.C. Choi, K.W. Kim, H.K. Jang, S.S. Kim and C.N. Whang, Electronic properties of ion implanted crystalline polymer thin film deposited by ionized cluster beam . . . B59/60 (1991) 1245
Choe, H.S., see Cho, S.J. . . . B59/60 (1991) 1245
Choi, B.S., see Lee, R.Y. . . . B59/60 (1991) 532
Choi, G.H., see Goltsev, V.P. . . . B59/60 (1991) 930
Choi, S.C., see Cho, S.J. . . . B59/60 (1991) 1245
Christie, W.H., see Golanski, A. . . . B59/60 (1991) 444
Chu, C.H. and L.J. Chen, Annealing behavior of low energy, high dose BF_2^+ implanted (001)Si . . . B59/60 (1991) 391
Chu, W.-K., see Yu, N. . . . B59/60 (1991) 1061
Chu, W.-K., J.R. Liu and Z.H. Zhang, Radiation effects of high-T_c superconductors . . . B59/60 (1991) 1447
Chu, W.K., see Yu, N. . . . B59/60 (1991) 1409
Clapham, L., see Laursen, T. . . . B59/60 (1991) 768
Clapham, L., T. Laursen, J.L. Whitton, R. Pascual and J.A. Jackman, The influence of rapid thermal annealing on oxygen implant profiles in copper . . . B59/60 (1991) 1404
Coad, J.P., see Zhu, J. . . . B59/60 (1991) 168
Cole, R.C., see Knudsen, J.F. . . . B59/60 (1991) 1067
Coleman, W.D., see Hubler, G.K. . . . B59/60 (1991) 268
Conrad, J.R., see Qiu, X. . . . B59/60 (1991) 951
Consiglieri, A.C., see Nielsen, B.R. . . . B59/60 (1991) 772
Constantine, C., see Pearton, S.J. . . . B59/60 (1991) 1015
Corbett, J.W., see Gerasimenko, N.N. . . . B59/60 (1991) 647
Corcoran, S., see Yu, N. . . . B59/60 (1991) 1061
Costantini, J.M., F. Brisard, J.L. Flament, D. Bourgault, L. Sinopoli and J.L. Uzureau, Effects of high-energy heavy ion bombardment on the electrical conductivity of yttrium iron garnet . . . B59/60 (1991) 600
Cotell, C.M., see Hubler, G.K. . . . B59/60 (1991) 268

Cowie, J.G., L.J. Lowder, R.J. Culbertson, W.E. Kosik and R. Brown, Reduced hydrogen embrittlement susceptibility in platinum implanted high strength steel . . . B59/60 (1991) 871
Cozzolino, C., see Xia, W. . . . B59/60 (1991) 491
Cozzolino, C., see Li, J. . . . B59/60 (1991) 989
Craig, M.M., see Giedd, R.E. . . . B59/60 (1991) 1253
Culbertson, R.J., see Williams, J.M. . . . B59/60 (1991) 845
Culbertson, R.J., see Cowie, J.G. . . . B59/60 (1991) 871
Custer, J.S., see Roorda, S. . . . B59/60 (1991) 344
Custer, J.S., see Schreutelkamp, R.J. . . . B59/60 (1991) 614

Da Silva, M.F., see Feuser, U. . . . B59/60 (1991) 1049
Da Silva, M.F., see Soares, J.C. . . . B59/60 (1991) 1090
Danilin, A.B., Yu.N. Erokhin and V.N. Mordkovich, Photostimulated defect–impurity reactions during ion bombardment of Si . . . B59/60 (1991) 985
DaSilva, M.F., see Nielsen, B.R. . . . B59/60 (1991) 772
Davenas, J. and P. Thevenard, Electronic structure characterization of ion beam modified polyimide by optical absorption and reflection . . . B59/60 (1991) 1249
Dearnaley, G., see Bedell, C.J. . . . B59/60 (1991) 245
DeKoven, B.M., see Was, G.S. . . . B59/60 (1991) 802
Dektyarev, S.V., see Ryabchikov, A.I. . . . B59/60 (1991) 124
Delafond, J., see Rivière, J.P. . . . B59/60 (1991) 237
Delafond, J., see Jaouen, C. . . . B59/60 (1991) 406
Delafond, J., see Rivière, J.P. . . . B59/60 (1991) 781
Demaree, J.D., G.S. Was and N.R. Sorensen, Oxide formation and anodic polarization behavior of thin films of amorphous and crystalline Fe–Cr–P alloys prepared by ion beam mixing . . . B59/60 (1991) 757
Deng Jianguo, see Yu Zengliang . . . B59/60 (1991) 705
Denissen, C.J.M., see Kobs, K. . . . B59/60 (1991) 746
Depta, D., see Niewöhner, L. . . . B59/60 (1991) 523
Derry, T.E., see Spits, R.A. . . . B59/60 (1991) 1366
Derryberry, S.L., R.A. Weeks, R.A. Weller and M. Mendenhall, Characterization of defects in amorphous SiO_2 implanted with oxygen ions . . . B59/60 (1991) 1320
Desport, J.E., see Bedell, C.J. . . . B59/60 (1991) 245
DeVore, C.E., see Rai, A.K. . . . B59/60 (1991) 280
Di Bona, A., see Valeri, S. . . . B59/60 (1991) 98
Diaz de la Rubia, T., see Averback, R.S. . . . B59/60 (1991) 709
Dietrich, H.B., see Moore, F.G. . . . B59/60 (1991) 978
Dietrich, H.B., see Moore, F.G. . . . B59/60 (1991) 1103
Dietz, V., P. Ehrhart, D. Guggi, H.-G. Haubold, W. Jäger, M. Prieler and W. Schilling, Influence of ion bombardment during deposition on microstructure of evaporated aluminum films . . . B59/60 (1991) 284
Dimigen, H., see Kobs, K. . . . B59/60 (1991) 746
Dinhut, J.F., see Rivière, J.P. . . . B59/60 (1991) 781
Dodd, A., see Nielsen, B.R. . . . B59/60 (1991) 772
Dodd, R.A., see Qiu, X. . . . B59/60 (1991) 951
Dodson, B.W., Chemical effects in sub-keV ion–solid interactions . . . B59/60 (1991) 481
Donnelly, S.E., see Orrman-Rossiter, K.G. . . . B59/60 (1991) 197
Donnelly, S.E., see Gordon, J.S. . . . B59/60 (1991) 312
Donnet, C., G. Marest, N. Moncoffre and J. Tousset, Effects of annealing environment on surface chemical phases of iron-implanted sintered alumina . . . B59/60 (1991) 1177
Donnet, C., G. Marest, N. Moncoffre, J. Tousset, A. Rahioui, C. Esnouf and M. Brunel, Copper, iron and zirconium implantation into polycrystalline α-Al_2O_3 . . . B59/60 (1991) 1205
Drako, V.M., see Goltsev, V.P. . . . B59/60 (1991) 823
Drzal, L.T., see Grummon, D.S. . . . B59/60 (1991) 1271
Du, A.-Y., see Zhang, B.-X. . . . B59/60 (1991) 434
Du, G., see Xu, X.L. . . . B59/60 (1991) 1267
Duckworth, D., see Ridgway, M.C. . . . B59/60 (1991) 164
Dugger, M.T., see Bourcier, R.J. . . . B59/60 (1991) 905
Dunlop, A., see Audouard, A. . . . B59/60 (1991) 414
Dupin, J.P., see Canut, B. . . . B59/60 (1991) 1211
Durand, H.-A., see Ito, K. . . . B59/60 (1991) 321

Eby, R.K., see Wang, L.M. . . . B59/60 (1991) 395
Ehrhart, P., see Dietz, V. . . . B59/60 (1991) 284

Eichinger, P., see Kallweit, R. . . . B59/60 (1991) 1288
El Khakani, M.A., see Tosello, C. . . . B59/60 (1991) 545
El Khakani, M.A., G. Marest, N. Moncoffre and J. Tousset, Thermal behavior of nitrogen and carbon implanted AISI 304L stainless steel . . . B59/60 (1991) 817
El Khakani, M.A., see Marest, G. . . . B59/60 (1991) 833
Elliman, R.G., see Ridgway, M.C. . . . B59/60 (1991) 454
Engemann, J., see Theirich, D. . . . B59/60 (1991) 336
Ensinger, W., see Wolf, G.K. . . . B59/60 (1991) 173
Ensinger, W., see Barth, M. . . . B59/60 (1991) 254
Ensinger, W., M. Kiuchi, Y. Horino, A. Chayahara, K. Fujii and M. Satou, The influence of thermodynamic phase stabilities on the formation of nitride phases of chromium and titanium by dynamic ion beam mixing . . . B59/60 (1991) 259
Ensinger, W., see Liu Xianghuai . . . B59/60 (1991) 851
Erdemir, A., see Bhattacharya, R.S. . . . B59/60 (1991) 788
Erokhin, Yu.N., see Danilin, A.B. . . . B59/60 (1991) 985
Esnouf, C., see Donnet, C. . . . B59/60 (1991) 1205
Etoh, K., see Ito, K. . . . B59/60 (1991) 321
Evtukhov, R.N., see Belykh, S.F. . . . B59/60 (1991) 72
Evtukhov, R.N., see Belykh, S.F. . . . B59/60 (1991) 106
Ewing, R.C., see Wang, L.M. . . . B59/60 (1991) 395

Fan, W.D. and W.Y. Wang, Dual implantation of Si^+, P^+ into GaAs . . . B59/60 (1991) 1086
Fang, F., see Xu, X.L. . . . B59/60 (1991) 1267
Fang, Y., see Rehn, L.E. . . . B59/60 (1991) 1463
Fang Qinxue, see Liu Xianghuai . . . B59/60 (1991) 851
Farlow, G.C., see Ramabadran, U.B. . . . B59/60 (1991) 637
Farlow, G.C., see Jensen, K. . . . B59/60 (1991) 643
Fattakhov, Y.V., I.B. Khaibullin and T.N. Vasil'yeva, The influence of the ion type on the anisotropic local melting of implanted silicon . . . B59/60 (1991) 1072
Feitag, R.K., see Hubler, G.K. . . . B59/60 (1991) 268
Feng, X., see Lau, W.M. . . . B59/60 (1991) 316
Ferber, H., G.B. Hoflund, C.K. Mount and S. Hoshino, Modification of amorphous bright chromium deposited (ABCD) films by nitrogen ion implantation . . . B59/60 (1991) 957
Ferleger, V.Kh., see Belykh, S.F. . . . B59/60 (1991) 65
Ferleger, V.Kh., see Belykh, S.F. . . . B59/60 (1991) 72
Fernandez, J.M., see Tosello, C. . . . B59/60 (1991) 545
Feuser, U., R. Vianden, E. Alves, M.F. da Silva, E. Szilagyi, F. Pászti and J.C. Soares, Vacancy–acceptor complexes in germanium produced by ion implantation . . . B59/60 (1991) 1049
Fichtner, P.F.P., W. Jäger, K. Radermacher and S. Mantl, Precipitate coarsening and Co redistribution after ion implantation in silicon . . . B59/60 (1991) 632
Fischer, W., see Liu Xianghuai . . . B59/60 (1991) 851
Flament, J.L., see Costantini, J.M. . . . B59/60 (1991) 600
Fleischer, E.L., see Norton, M. G. . . . B59/60 (1991) 1215
Follstaedt, D.M., see Knapp, J.A. . . . B59/60 (1991) 742
Follstaedt, D.M., see Bourcier, R.J. . . . B59/60 (1991) 905
Follstaedt, D.M., S.M. Myers and R.J. Bourcier, Microstructures of cubic Al_2O_3 precipitates in oxygen-implanted aluminum . . . B59/60 (1991) 909
Fontenille, J., see Benyagoub, A. . . . B59/60 (1991) 418
Foo, K.K., see Lau, W.M. . . . B59/60 (1991) 316
Foti, G., see Calcagno, L. . . . B59/60 (1991) 1153
Frey, L., see Öchsner, R. . . . B59/60 (1991) 793
Fuchs, G., see Audouard, A. . . . B59/60 (1991) 414
Fuchs, G., see Romana, L. . . . B59/60 (1991) 567
Fuchs, G., see Abonneau, E. . . . B59/60 (1991) 1183
Fujihana, T., see Kobayashi, K. . . . B59/60 (1991) 467
Fujihana, T., A. Sekiguchi, K. Takahashi and M. Iwaki, Electrochemical properties of high-dose carbon-implanted iron . . . B59/60 (1991) 764
Fujii, K., see Horino, Y. . . . B59/60 (1991) 139
Fujii, K., see Ensinger, W. . . . B59/60 (1991) 259
Fujii, K., see Yoshida, Y. . . . B59/60 (1991) 962
Fujimoto, F., see Ogata, K. . . . B59/60 (1991) 225
Fujimoto, F., see Ogata, K. . . . B59/60 (1991) 229
Fujimoto, F., see Nakane, Y. . . . B59/60 (1991) 264

Fujimoto, F., see Andoh, Y. . . . B59/60 (1991) 276
Fukui, Y., O. Nishimura, K. Yabe and M. Iwaki, XPS study of iron surface layers implanted with both titanium and nitrogen . . . B59/60 (1991) 812
Funk, L., see Woo, J.J. . . . B59/60 (1991) 537
Furubayashi, B., see Sakamoto, I. . . . B59/60 (1991) 900
Furukawa, S., see Ohta, K. . . . B59/60 (1991) 1113
Furuya, T., see Sugizaki, Y. . . . B59/60 (1991) 722

Gagnon, G., see Trudeau, Y.B. . . . B59/60 (1991) 609
Gagnon, G., see Touhouche, K. . . . B59/60 (1991) 676
Galloway, M.D., see Zuhr, R.A. . . . B59/60 (1991) 308
Galloway, M.D., see Golanski, A. . . . B59/60 (1991) 444
Galuska, A.A., Mechanisms of adhesion enhancement using reactive ion mixing . . . B59/60 (1991) 487
Gamo, K. and S. Namba, Recent advance of focused ion beam technology in maskless deposition and patterning B59/60 (1991) 190
Gao Yuzun, see Zhang Tonghe . . . B59/60 (1991) 828
Gea, L., see Ramos, S.M.M. . . . B59/60 (1991) 1201
Gea, L., see Canut, B. . . . B59/60 (1991) 1211
Geerk, J., see Linker, G. . . . B59/60 (1991) 1458
Gerasimenko, N.N., V.F. Stas and J.W. Corbett, Inactivation of implanted impurities during buried Si_3N_4 layer formation . . . B59/60 (1991) 647
Gerritsen, E., see Kobs, K. . . . B59/60 (1991) 746
Giedd, R.E., see Bridwell, L.B. . . . B59/60 (1991) 1240
Giedd, R.E., M.G. Moss, M.M. Craig and D.E. Robertson, Temperature sensitive ion-implanted polymer films . B59/60 (1991) 1253
Gillin, W.P., see Soares, J.C. . . . B59/60 (1991) 1090
Ginley, D.S., see Barbour, J.C. . . . B59/60 (1991) 1395
Girardeau, T., see Rivière, J.P. . . . B59/60 (1991) 781
Glick, S., see Williamson, D.L. . . . B59/60 (1991) 737
Godbole, V.P., see Ogale, S.B. . . . B59/60 (1991) 1350
Godefroy, G., see Moretti, P. . . . B59/60 (1991) 1228
Goktepe, O.F., A statistical comparison of Monte Carlo codes TRIM and EVOLVE . . . B59/60 (1991) 28
Goktepe, O.F., J.M. Lambert and A.M. Vincenz, Sputtering yields calculations of thin gold films bombarded with 175 keV argon ions – effects of surface binding and displacement threshold energies . . . B59/60 (1991) 33
Golanski, A., W.H. Christie, M.D. Galloway, J.L. Park, S.J. Pennycook, D.B. Poker, J.L. Moore, H.E. Harmon and C.W. White, Ion beam induced diffusion and crystallization in high-dose Er implanted Si . . . B59/60 (1991) 444
Goltsev, V.P., V.V. Khodasevich, I.I. Prikhodko and V.V. Uglov, The phase formation in bilayered Zr/Ni thin-film system made by atomic mixing . . . B59/60 (1991) 558
Goltsev, V.P., V.V. Khodasevich, A.K. Kuleshov and V.V. Uglov, Defect formation and structure in Fe films irradiated successively by nitrogen and boron ions . . . B59/60 (1991) 751
Goltsev, V.P., V.M. Drako, V.V. Uglov, V.V. Khodasevich and M. Soukieh, The formation of amorphous structure during irradiation of Fe–30% Ni alloy by phosphorus ions . . . B59/60 (1991) 823
Goltsev, V.P., V.V. Khodasevich, G.H. Choi and V.V. Uglov, Ion induced changes of physical–mechanical properties in Al alloys . . . B59/60 (1991) 930
Gonzales, A., see Williams, J.M. . . . B59/60 (1991) 845
Goossen, K.W., see White, A.E. . . . B59/60 (1991) 693
Gordon, J.S., D.G. Armour, S.E. Donnelly, J.A. van den Berg, D. Marton and J.W. Rabalais, A dual-source low-energy mass-analysed ion beam system for semiconductor epitaxy and novel materials growth . . . B59/60 (1991) 312
Grande, P.L., see Behar, M. . . . B59/60 (1991) 1
Gratton, L.M., A. Miotello, C. Tosello, D.C. Kothari, G. Principi and A. Tomasi, Ion-beam mixing of Al–Fe multilayer films . . . B59/60 (1991) 541
Gratton, L.M., see Tosello, C. . . . B59/60 (1991) 545
Grummon, D.S., R. Schalek, A. Ozzello, J. Kalantar and L.T. Drzal, High-energy ion implantation of polymeric fibers for modification of reinforcement-matrix adhesion . . . B59/60 (1991) 1271
Gu, X., see Kikkawa, S. . . . B59/60 (1991) 341
Guerlin, T., see Rübesame, D. . . . B59/60 (1991) 80
Guesdon, Ph., see Rivière, J.P. . . . B59/60 (1991) 237
Guggi, D., see Dietz, V. . . . B59/60 (1991) 284
Guggina, W.H., D.G. Ballegeer and I. Adesida, Effects of reactive ion etching on GaAs/AlGaAs heterostructures B59/60 (1991) 1011
Gupta, A., see Tosello, C. . . . B59/60 (1991) 545

Haglund Jr, R.F., see Becker, K. . . . B59/60 (1991) 1304
Hagmann, D.R., W. Xi and R.E. Hummel, A study of the solid phase epitaxial regrowth of amorphous silicon utilizing differential reflectometry . . . B59/60 (1991) 110

Hamelin, N., see Babsail, L. . . . B59/60 (1991) 1219
Han, C.C., see Xia, W. . . . B59/60 (1991) 491
Handy, B.N., see Antolak, A.J. . . . B59/60 (1991) 13
Hanke, R., H. Knapp, D. Rübesame, S. Wege and H. Niedrig, A capillaritron ion source as triode system coupled with an einzel lens . . . B59/60 (1991) 135
Han Ying, see Tan Hui . . . B59/60 (1991) 785
Hardtke, Ch., W. Schilling and H. Ullmaier, Influence of particle bombardment on microstructure and internal stresses of refractory metal silicides on silicon . . . B59/60 (1991) 377
Harmon, H.E., see Golanski, A. . . . B59/60 (1991) 444
Hart, R.R., R.P. Vijay and J.D. Rubio, Ar ion beam induced recrystallization of amorphous layers in thin Si films B59/60 (1991) 427
Hartmann, D., see Mantl, S. . . . B59/60 (1991) 666
Hasegawa, M., see Kobayashi, N. . . . B59/60 (1991) 449
Hashimoto, M., see Chayahara, A. . . . B59/60 (1991) 893
Hashimoto, Y., see Yamada, I. . . . B59/60 (1991) 216
Haubold, H.-G., see Dietz, V. . . . B59/60 (1991) 284
Hayashi, N., see Kobayashi, N. . . . B59/60 (1991) 449
Hayashi, N., I. Sakamoto, N. Kobayashi, H. Kobayashi and E. Johnson, The effect of Xe ion irradiation in 17/13 single-crystalline austenitic stainless steel . . . B59/60 (1991) 897
Hayashi, N., see Sakamoto, I. . . . B59/60 (1991) 900
Hayashi, N., see Kuriyama, K. . . . B59/60 (1991) 1116
Haynes, T.E., see Zuhr, R.A. . . . B59/60 (1991) 308
Haynes, T.E. and O.W. Holland, Dose rate effects on damage formation in ion-implanted gallium arsenide . . . B59/60 (1991) 1028
Hecking, N., Ranges and electronic stopping powers of 1–20 MeV ^{28}Si ions in Si targets as obtained from optical reflectivity measurements on bevelled samples . . . B59/60 (1991) 619
Heiland, W., see Niehof, A. . . . B59/60 (1991) 1355
He Jianjun, see Yu Zengliang . . . B59/60 (1991) 705
Hellman, O.C., see Herbots, N. . . . B59/60 (1991) 326
Herbots, N., O. Vancauwenberghe, O.C. Hellman and Y.C. Joo, Atomic collisions, elastic recombination, and thermal diffusion during thin-film growth from low-energy ion beams . . . B59/60 (1991) 326
Hertl, W., see Norton, M. G. . . . B59/60 (1991) 1215
Higeta, K., see Yoshida, Y. . . . B59/60 (1991) 962
Hirayama, H., G.H. Takaoka, H. Usui and I. Yamada, Low temperature homo- and hetero-epitaxy of sapphire films by reactive ionized cluster beam deposition . . . B59/60 (1991) 207
Hirayama, N., see Koshida, N. . . . B59/60 (1991) 1292
Hirvonen, J.-P., see Nastasi, M. . . . B59/60 (1991) 806
Hobson, W.S., see Pearton, S.J. . . . B59/60 (1991) 1015
Hoffmann, V., see Barth, M. . . . B59/60 (1991) 254
Hoflund, G.B., see Ferber, H. . . . B59/60 (1991) 957
Holland, O.W. and C.W. White, Ion-induced damage and amorphization in Si . . . B59/60 (1991) 353
Holland, O.W., see Haynes, T.E. . . . B59/60 (1991) 1028
Holländer, B., see Li, J. . . . B59/60 (1991) 989
Holländer, B., S. Mantl, B. Stritzker and R. Butz, Ion scattering studies of diffusion and strain relaxation in $Si/Si_{1-x}Ge_x$ superlattices . . . B59/60 (1991) 994
Holmes, A.J.T., see Surrey, E. . . . B59/60 (1991) 128
Homma, Y., see Tanaka, T. . . . B59/60 (1991) 116
Honda, Y., see Nakane, Y. . . . B59/60 (1991) 264
Hong, Q.Z., see Li, J. . . . B59/60 (1991) 989
Hoondert, W.H.B., see Huijgen, T.P. . . . B59/60 (1991) 150
Hoondert, W.H.B., see Seijbel, L.J. . . . B59/60 (1991) 1336
Hoondert, W.H.B., W.Th.M. Buters, B.J. Thijsse and A. van den Beukel, Defect studies on nonstoichiometric TiN by THDS . . . B59/60 (1991) 1340
Horie, H., see Saito, Y. . . . B59/60 (1991) 1173
Horino, Y., A. Chayahara, M. Kiuchi, K. Fujii, M. Satou and M. Takai, A focused MeV heavy ion beam line for materials modification and microanalysis . . . B59/60 (1991) 139
Horino, Y., see Ensinger, W. . . . B59/60 (1991) 259
Horino, Y., see Matthews, A.P. . . . B59/60 (1991) 671
Hoshino, S., see Ferber, H. . . . B59/60 (1991) 957
Hou, P.Y., I.G. Brown and J. Stringer, Study of the effect of reactive-element addition by implanting metal ions in a preformed oxide layer . . . B59/60 (1991) 1345
Howe, L.M., D.P. McCooeye, M.H. Rainville, J.D. Bonnett and D. Phillips, Ion bombardment of Zr_3Fe . . . B59/60 (1991) 884
Hsieh, H. and R.S. Averback, Atomic size effect on the formation of ionized cluster beam epitaxy in Lennard–Jones systems . . . B59/60 (1991) 203

Hsieh, H., see Averback, R.S. B59/60 (1991) 709
Hsieh, Y.-F., see White, A.E. B59/60 (1991) 693
Hsu, S.N., see Xia, W. B59/60 (1991) 491
Hsu, S.N., see Li, J. B59/60 (1991) 989
Hsu, S.N., L.J. Chen and S.S. Lau, Effects of substrate temperature on the annealing behavior of residual defects in high-dose As^+ implanted (001) Si B59/60 (1991) 1037
Hsu, T.M., see Huang, F.S. B59/60 (1991) 1003
Hu, Y.Z., J.W. Andrews, M. Li and E.A. Irene, In situ spectroscopic ellipsometric investigation of argon ion bombardment of single-crystal silicon and silicon dioxide films B59/60 (1991) 76
Huang, F.S., W.S. Chen, T.M. Hsu and C.W. Lee, Rapid thermal annealing of the through-film silicon implantation on GaAs B59/60 (1991) 1003
Huang, H.Z., see Pan, X.Z. B59/60 (1991) 233
Huang, J.S., Carbide formation in Nb and Ta implanted by carbon ions at room temperature B59/60 (1991) 651
Huang Wei, see Wang Xi B59/60 (1991) 272
Hubler, G.K., C.A. Carosella, P.G. Burkhalter, R.K. Feitag, C.M. Cotell and W.D. Coleman, Fabrication of low-Z X-ray mirrors by ion beam assisted deposition B59/60 (1991) 268
Hubler, G.K., see Natishan, P.M. B59/60 (1991) 841
Huijgen, T.P., W.H.B. Hoondert, L.J. Seijbel, B.J. Thijsse and A. van den Beukel, An apparatus for combined ion-beam assisted deposition and thermal desorption spectrometry B59/60 (1991) 150
Huijgen, T.P., see Seijbel, L.J. B59/60 (1991) 1336
Hull, R., see White, A.E. B59/60 (1991) 693
Hummel, R.E., see Hagmann, D.R. B59/60 (1991) 110
Hummel, R.E., D. Malone and H. Kawasaki, Electromigration and contact filling of aluminum films deposited by ion-enhanced processes B59/60 (1991) 297
Huo Yuping, see Yu Zengliang B59/60 (1991) 705

Ikuni, S., see Adachi, M. B59/60 (1991) 940
Im, J.S., see Atwater, H.A. B59/60 (1991) 386
Im, J.S. and H.A. Atwater, Kinetic and thermodynamic enhancement of crystal nucleation and growth rates in amorphous Si film during ion irradiation B59/60 (1991) 422
Imada, K., see Kawagoe, Y. B59/60 (1991) 1426
Inoue, N., M. Kikuchi, T. Manabe, T. Shima and Y. Nishi, Effect of ion treatment on water wettability of SiO_2 glass B59/60 (1991) 1328
Inoue, N., see Nishi, Y. B59/60 (1991) 1415
Inoue, N., see Nishi, Y. B59/60 (1991) 1418
Inoue, T., see Yoshida, Y. B59/60 (1991) 962
Inoue, Y., see Yamada, I. B59/60 (1991) 219
Irene, E.A., see Hu, Y.Z. B59/60 (1991) 76
Ishida, S., see Yamazaki, H. B59/60 (1991) 981
Ito, H., see Yamazaki, H. B59/60 (1991) 981
Ito, K., T. Yonemitsu, K. Etoh, H. Sekiguchi, I. Yamada, I. Kataoka and H.-A. Durand, Evaluation of thin films fabricated by low energy direct ion beam deposition for soft X-rays B59/60 (1991) 321
Itoh, K., see Nishi, Y. B59/60 (1991) 1422
Itoh, Y., see Yamada, I. B59/60 (1991) 216
Iwaki, M., see Kobayashi, K. B59/60 (1991) 467
Iwaki, M., see Matthews, A.P. B59/60 (1991) 671
Iwaki, M., see Suzuki, Y. B59/60 (1991) 698
Iwaki, M., see Fujihana, T. B59/60 (1991) 764
Iwaki, M., see Fukui, Y. B59/60 (1991) 812
Iwaki, M., see Suzuki, Y. B59/60 (1991) 1300
Iwaki, M., see Sato, S. B59/60 (1991) 1391
Iwamoto, K., see Kanno, I. B59/60 (1991) 920

Jackman, J.A., see Laursen, T. B59/60 (1991) 768
Jackman, J.A., see Clapham, L. B59/60 (1991) 1404
Jackson, H.E., see Ramabadran, U.B. B59/60 (1991) 637
Jacobson, D.C., see Roorda, S. B59/60 (1991) 344
Jacobson, D.C., see White, A.E. B59/60 (1991) 693
Jacobson, D.C., see Polman, A. B59/60 (1991) 1313
Jäger, W., see Dietz, V. B59/60 (1991) 284
Jäger, W., see Fichtner, P.F.P. B59/60 (1991) 632
Jahnke, T., see Bridwell, L.B. B59/60 (1991) 1240
Jain, A.K., see Salvi, V.P. B59/60 (1991) 1124

Janeczek, J., see Wang, L.M. B59/60 (1991) 395
Jang, H.K., see Cho, S.J. B59/60 (1991) 1245
Janssen, K.T.F., see Raineri, V. B59/60 (1991) 1056
Jaouen, C., J.P. Rivière and J. Delafond, Temperature dependence for ion-induced amorphization of NiAl . . B59/60 (1991) 406
Jaouen, M., see Rivière, J.P. B59/60 (1991) 781
Jarrold, M.F., see Brown, W.L. B59/60 (1991) 182
Jebasinski, R., see Mantl, S. B59/60 (1991) 666
Jenčič, I., M.W. Bench, I.M. Robertson, M.A. Kirk and J. Peternelj, A comparison of the rates of amorphization in the $Al_xGa_{1-x}As$/GaAs system B59/60 (1991) 458
Jensen, K. and G.C. Farlow, Analysis of RBS spectra from samples implanted to high dose B59/60 (1991) 643
Jeong, H.-S., Z. Lu and R.C. White, Surface modification of polyimide by ECR plasma B59/60 (1991) 1285
Jervis, T.R., see Nastasi, M. B59/60 (1991) 806
Ji Chengzhou, see Zhang Tonghe B59/60 (1991) 828
Jie, Z.-Z., see Li, J.-C. B59/60 (1991) 1110
Johansen, A., see Sarholt-Kristensen, L. B59/60 (1991) 85
Johnson, D., see Pearton, S.J. B59/60 (1991) 1015
Johnson, E., see Sarholt-Kristensen, L. B59/60 (1991) 85
Johnson, E., see Hayashi, N. B59/60 (1991) 897
Johnson, S.T., see Ridgway, M.C. B59/60 (1991) 164
Johnson, S.T., see Ridgway, M.C. B59/60 (1991) 454
Jones, K.S., see Venables, D. B59/60 (1991) 1019
Joo, Y.C., see Herbots, N. B59/60 (1991) 326
Jousset, J.C., see Audouard, A. B59/60 (1991) 414

Kaim, R.E., see Raineri, V. B59/60 (1991) 1056
Kajrys, G., see Touhouche, K. B59/60 (1991) 676
Kajrys, G.E., see Trudeau, Y.B. B59/60 (1991) 609
Kalantar, J., see Grummon, D.S. B59/60 (1991) 1271
Kalbitzer, S., see Liu Xianghuai B59/60 (1991) 851
Kalitzova, M., see Vitali, G. B59/60 (1991) 1077
Kallweit, R., M. Baur, P. Eichinger and H. Strack, SIMS investigation of ion implanted PMMA B59/60 (1991) 1288
Kamei, M., see Yoshida, I. B59/60 (1991) 1443
Kamenitsa, D.E., see Park, C. B59/60 (1991) 159
Kanamaru, F., see Kikkawa, S. B59/60 (1991) 341
Kanetkar, S.M., see Ogale, S.B. B59/60 (1991) 1350
Kang, S.T., see Lee, R.Y. B59/60 (1991) 532
Kanno, I., K. Nomoto, S. Nishijima, T. Nishiura, T. Okada, K. Katagiri, H. Mori and K. Iwamoto, Tribological properties of aluminum modified with nitrogen ion implantation and plasma treatment B59/60 (1991) 920
Kant, R.A. and B.D. Sartwell, The effect of chlorine on the sputter/etch rate of nickel B59/60 (1991) 89
Karmarkar, M.M., see Auner, G.W. B59/60 (1991) 504
Karmarkar, M.M., see Cheng, Y.-T. B59/60 (1991) 509
Karpuzov, D., see Vitali, G. B59/60 (1991) 1077
Karpuzov, D.S., see Budinov, H.I. B59/60 (1991) 1041
Kaschny, J.R., L. Amaral and M. Behar, Low-temperature diffusion study of Xe implanted into a polymer film . B59/60 (1991) 1281
Kastner, J., see Palmetshofer, L. B59/60 (1991) 1081
Katagiri, K., see Kanno, I. B59/60 (1991) 920
Kataoka, I., see Ito, K. B59/60 (1991) 321
Katardjiev, I., see Vitali, G. B59/60 (1991) 1077
Katayama, S., see Kikkawa, S. B59/60 (1991) 341
Katayama, S., see Yokota, K. B59/60 (1991) 1431
Kawagoe, Y., K. Yamanishi, M. Tanaka, K. Imada and K. Sato, Formation of superconducting Er–Ba–Cu–O thin films by ionized cluster beam apparatus B59/60 (1991) 1426
Kawakami, M., see Nishi, Y. B59/60 (1991) 1422
Kawasaki, H., see Hummel, R.E. B59/60 (1991) 297
Keeley, J., see Wu, R.L.C. B59/60 (1991) 1232
Kellock, A.J., J.E.E. Baglin, T.T. Bardin and J.G. Pronko, Adhesion improvement of Au on GaAs using ion beam assisted deposition B59/60 (1991) 249
Kelly, R. and A. Miotello, On the application of Darken's analysis to ion-beam mixing B59/60 (1991) 517
Keune, W., see Tosello, C. B59/60 (1991) 545
Khaibullin, I.B., see Fattakhov, Y.V. B59/60 (1991) 1072
Khodasevich, V.V., see Goltsev, V.P. B59/60 (1991) 558
Khodasevich, V.V., see Goltsev, V.P. B59/60 (1991) 751

Khodasevich, V.V., see Goltsev, V.P. B59/60 (1991) 823
Khodasevich, V.V., see Goltsev, V.P. B59/60 (1991) 930
Kikkawa, S., M. Takahashi, X. Gu, F. Kanamaru, S. Katayama and M. Koizumi, Rf-sputter deposition of boron nitride thin films B59/60 (1991) 341
Kikuchi, M., see Inoue, N. B59/60 (1991) 1328
Kim, H.K., S.O. Kim, J.H. Song, K.W. Kim, J.J. Woo, C.N. Wang and R.J. Smith, Ar^+ induced interfacial mixing and phase formation in the Al/Cr system B59/60 (1991) 554
Kim, K.W., see Lee, R.Y. B59/60 (1991) 532
Kim, K.W., see Kim, H.K. B59/60 (1991) 554
Kim, K.W., see Cho, S.J. B59/60 (1991) 1245
Kim, S.O., see Kim, H.K. B59/60 (1991) 554
Kim, S.S., see Cho, S.J. B59/60 (1991) 1245
Kinder, J., see Nielsen, B.R. B59/60 (1991) 772
King, B.V., S.G. Puranik and R.J. MacDonald, Low-energy ion mixing in zirconium B59/60 (1991) 550
Kingon, A.I., see Soble II, C.N. B59/60 (1991) 155
Kinser, D.L., see Wang, P.W. B59/60 (1991) 1317
Kirimura, H., see Andoh, Y. B59/60 (1991) 276
Kirk, M.A., see Bench, M.W. B59/60 (1991) 372
Kirk, M.A., see Jenčič, I. B59/60 (1991) 458
Kirschbaum, C., see Yu, N. B59/60 (1991) 1061
Kitamoto, S., see Yamada, I. B59/60 (1991) 216
Kitamura, M., see Yamada, I. B59/60 (1991) 219
Kitoh, K., see Matsunami, N. B59/60 (1991) 5
Kiuchi, M., see Horino, Y. B59/60 (1991) 139
Kiuchi, M., see Ensinger, W. B59/60 (1991) 259
Kiuchi, M., see Miyano, T. B59/60 (1991) 1167
Kiyama, S., see Chayahara, A. B59/60 (1991) 893
Klassen, T., see Lindner, J.K.N. B59/60 (1991) 655
Klein, K.M., C. Park and A.F. Tasch, Modeling of cumulative damage effects on ion-implantation profiles . . . B59/60 (1991) 60
Klein, K.M., see Park, C. B59/60 (1991) 159
Klein, P.B., see Moore, F.G. B59/60 (1991) 1103
Kluge, A., see Schork, R. B59/60 (1991) 499
Kluge, A., see Langguth, K. B59/60 (1991) 718
Kluge, A., see Kobs, K. B59/60 (1991) 746
Kluge, A., see Öchsner, R. B59/60 (1991) 793
Knapp, H., D. Rübesame and H. Niedrig, Production of needle-type liquid-metal ion sources and their application in a scanning ion microscope B59/60 (1991) 131
Knapp, H., see Hanke, R. B59/60 (1991) 135
Knapp, J.A., D.M. Follstaedt, N.R. Sorensen and L.E. Pope, Amorphization of C-implanted Fe(Cr) alloys . . . B59/60 (1991) 742
Knudsen, J.F., P.M. Adams, D.L. Leung, R.C. Cole and D.C. Mayer, X-ray, XTEM and RBS analysis of recrystallized ion beam amorphized CVD Si B59/60 (1991) 1067
Ko, K.-Y., see Lee, S.-T. B59/60 (1991) 999
Ko, K.Y., see Braunstein, G. B59/60 (1991) 1032
Kobayashi, H., see Masaki, S. B59/60 (1991) 292
Kobayashi, H., see Kobayashi, N. B59/60 (1991) 449
Kobayashi, H., see Hayashi, N. B59/60 (1991) 897
Kobayashi, K., M. Iwaki and T. Fujihana, Correlation between energy deposition and AlN crystal growth induced by ion bombardment B59/60 (1991) 467
Kobayashi, N., M. Hasegawa, H. Kobayashi, N. Hayashi, M. Shinohara, F. Ohtani and M. Asari, Ion-beam-induced epitaxial crystallization of amorphous GaAs on GaAs(100) B59/60 (1991) 449
Kobayashi, N., see Hayashi, N. B59/60 (1991) 897
Kobs, K., H. Dimigen, C.J.M. Denissen, E. Gerritsen, J. Politiek, R. Oechsner, A. Kluge and H. Ryssel, Strong wear reduction of high-dose carbon-implanted AISI 52100 steel B59/60 (1991) 746
Koike, J., P.R. Okamoto, L.E. Rehn and M. Meshii, Correlation between the elastic shear instability mechanism and empirical criteria for irradiation-induced amorphization B59/60 (1991) 471
Koinkar, V.N., see Ogale, S.B. B59/60 (1991) 1350
Koizumi, M., see Kikkawa, S. B59/60 (1991) 341
Komori, S., see Tsukamoto, K. B59/60 (1991) 584
Koponen, I., Computer studies of nonstoichiometric recoil production in binary compounds B59/60 (1991) 41
Koshida, N. and H. Yabumoto, Effects of ion implantation on the photoelectrochemical properties of TiO_2 . . B59/60 (1991) 1236
Koshida, N. and N. Hirayama, Ion implantation induced change in fibrillar morphology of polyacetylene films . B59/60 (1991) 1292
Kosik, W.E., see Cowie, J.G. B59/60 (1991) 871

Kothari, D.C., see Gratton, L.M. . . . B59/60 (1991) 541
Kramer, K.M., J.R. Tesmer and M. Nastasi, Oxidation studies of yttrium implanted copper, molybdenum and tantalum using high-energy resonant helium backscattering . . . B59/60 (1991) 865
Krauss, A.R., see Soble II, C.N. . . . B59/60 (1991) 155
Kroener, T., see Linker, G. . . . B59/60 (1991) 1458
Kubo, M. and T. Narusawa, Effects of low energy ion bombardment on GaAs molecular beam epitaxy . . . B59/60 (1991) 332
Kuldeep, see Salvi, V.P. . . . B59/60 (1991) 1124
Kuleshov, A.K., see Goltsev, V.P. . . . B59/60 (1991) 751
Kura, T., see Yokota, K. . . . B59/60 (1991) 1431
Kuriyama, K., M. Tsugita and N. Hayashi, Structural and electrical properties of Si layers implanted with various Ge ion doses . . . B59/60 (1991) 1116
Kuroi, T., see Tsukamoto, K. . . . B59/60 (1991) 584
Kurokawa, M., see Chayahara, A. . . . B59/60 (1991) 893
Kurosawa, S., see Tanaka, T. . . . B59/60 (1991) 116
Kusakabe, K., see Suzuki, Y. . . . B59/60 (1991) 698
Kusakabe, M., see Suzuki, Y. . . . B59/60 (1991) 698
Kusakabe, M., see Suzuki, Y. . . . B59/60 (1991) 1300

Lam, N.Q., see Yacout, A.M. . . . B59/60 (1991) 57
Lam, N.Q., S. Tang, A.M. Yacout, L.E. Rehn and J.F. Stubbins, Ion beam modifications of near-surface compositions in ternary alloys . . . B59/60 (1991) 889
Lambert, J.M., see Goktepe, O.F. . . . B59/60 (1991) 33
Langguth, K., A. Kluge and H. Ryssel, Characterization and wear tests of steel surfaces implanted with oxygen, aluminum, and carbon dioxide . . . B59/60 (1991) 718
Langouche, G., see Vantomme, A. . . . B59/60 (1991) 680
Lau, S.S., see Xia, W. . . . B59/60 (1991) 491
Lau, S.S., see Li, J. . . . B59/60 (1991) 989
Lau, S.S., see Hsu, S.N. . . . B59/60 (1991) 1037
Lau, W.M., X. Feng, I. Bello, S. Sant, K.K. Foo and R.P.W. Lawson, Construction, characterization and applications of a compact mass-resolved low-energy ion beam system . . . B59/60 (1991) 316
Laugier, M.T., Effects of B^+ implantation on Palmqvist and Hertzian indentation response of Ti coated glass . B59/60 (1991) 943
Laursen, T., L. Clapham, J.L. Whitton and J.A. Jackman, The effect of ion-implanted yttrium on the oxidation of austenitic stainless steel . . . B59/60 (1991) 768
Laursen, T., see Clapham, L. . . . B59/60 (1991) 1404
Lawrence, D., see Braunstein, G. . . . B59/60 (1991) 1032
Lawson, R.P.W., see Lau, W.M. . . . B59/60 (1991) 316
Le Brusq, J., see Ramos, S.M.M. . . . B59/60 (1991) 1201
Lee, C.W., see Huang, F.S. . . . B59/60 (1991) 1003
Lee, I.-S., see Williams, J.M. . . . B59/60 (1991) 845
Lee, R.Y., B.S. Choi, J.H. Song, K.W. Kim, S.T. Kang, C.N. Whang and R.J. Smith, The effect of Ar^+ irradiation on grain growth and reducing reaction temperature in Pd-silicide formation . . . B59/60 (1991) 532
Lee, S.-T., S. Chen, G. Braunstein, K.-Y. Ko and T.Y. Tan, Anomalous electrical activation in Si-implanted GaAs/AlGaAs superlattices . . . B59/60 (1991) 999
Lee, S.-T., see Braunstein, G. . . . B59/60 (1991) 1032
Lesueur, D., see Audouard, A. . . . B59/60 (1991) 414
Leung, D.L., see Knudsen, J.F. . . . B59/60 (1991) 1067
Levy, M., see Williams, J.M. . . . B59/60 (1991) 845
Li, H.-D., see Min, Z. . . . B59/60 (1991) 1358
Li, J., Q.Z. Hong, G. Vizkelethy, J.W. Mayer, C. Cozzolino, W. Xia, B. Zhu, S.N. Hsu, S.S. Lau, B. Holländer, R. Butz and S. Mantl, Ion mixing in amorphous and crystalline Si/Ge layered structures . . . B59/60 (1991) 989
Li, J.-C., B.-H. Xia, X.-G. Wu, Z.-Z. Jie, X.-Z. Pan and Y.-W. Xiao, Low-energy H_2^+ implantation effects on the characteristics of polysilicon solar cells . . . B59/60 (1991) 1110
Li, J.M., Proton-implanted new type silicon material subjected to two-step furnace annealing . . . B59/60 (1991) 1053
Li, M., see Hu, Y.Z. . . . B59/60 (1991) 76
Li, Q., see Zhang, B.-X. . . . B59/60 (1991) 434
Li, W.-Z., see Min, Z. . . . B59/60 (1991) 1358
Li, X.N., see Zhu, J.L. . . . B59/60 (1991) 1045
Lidgard, A., see Polman, A. . . . B59/60 (1991) 1313
Liefting, J.R., see Schreutelkamp, R.J. . . . B59/60 (1991) 614
Lifanova, L.F. and R.U. Almuratov, Modification of coatings by low-energy argon ion bombardment during their growth and its influence on thermo-enhanced release of argon . . . B59/60 (1991) 241
Ligeon, E., see Benyagoub, A. . . . B59/60 (1991) 418

Li Jinhua, Lin Chenglu, Lin Zhixing, Zhou Zuyao and Zou Shichang, Stability of SIMOX and SIMNI structures at high temperature in hydrogen . . . B59/60 (1991) 685
Lilienfeld, D.A., see Børgesen, P. . . . B59/60 (1991) 563
Lin, C.L., see Zhang, S.K. . . . B59/60 (1991) 690
Lin, S.H., K.L. Sheng, T.W. Rong, J.R. Bao, W.M. Wang, H.H. Wan, Z.Y. Zhou, X.F. Zhu and F.J. Yang, Electrical properties of chemical-doped and ion-implanted polyacetylene films . . . B59/60 (1991) 1257
Lin, X., see Zhu, J.L. . . . B59/60 (1991) 1045
Lin, Z.X., see Xu, X.L. . . . B59/60 (1991) 1267
Lin Chenglu, see Li Jinhua . . . B59/60 (1991) 685
Lin Chenglu, see Tan Hui . . . B59/60 (1991) 785
Lindner, J.K.N., T. Klassen and E.H. te Kaat, Ion beam synthesis of deep buried $NiSi_2$ layers in silicon by 6 MeV Ni implantation . . . B59/60 (1991) 655
Linker, G., J. Geerk, T. Kroener, O. Meyer, J. Remmel, R. Smithey, B. Strehlau and X.X. Xi, Superconductivity and structure of ion-irradiated high-temperature superconductor thin films . . . B59/60 (1991) 1458
Lin Zhixing, see Li Jinhua . . . B59/60 (1991) 685
Li Shizhuo, see Chen Yuanru . . . B59/60 (1991) 1295
Liu, B.-X., Ion-mixing-induced fractal growth in thin alloy films . . . B59/60 (1991) 475
Liu, J.L., see Zhang, T.Q. . . . B59/60 (1991) 1007
Liu, J.R., see Chu, W.-K. . . . B59/60 (1991) 1447
Liu Hong, see Chen Yuanru . . . B59/60 (1991) 1295
Liu Xianghuai, see Wang Xi . . . B59/60 (1991) 272
Liu Xianghuai, Zou Shichang, S. Taniguchi, Fang Qinxue, S. Kalbitzer, A. Schröer, W. Fischer, M. Barth, W. Ensinger and G.K. Wolf, Electrochemical characterization and corrosion behaviour of Ni_3Al (0.1B) modified by ion beam techniques: a comparative study . . . B59/60 (1991) 851
Lo Russo, S., see Tosello, C. . . . B59/60 (1991) 545
Lombardo, S., see Spinella, C. . . . B59/60 (1991) 363
Lowder, L.J., see Cowie, J.G. . . . B59/60 (1991) 871
Lu, W.X., see Schreutelkamp, R.J. . . . B59/60 (1991) 614
Lu, Y.F., M. Takai, S. Namba, H. Sanda, A. Chayahara and M. Satou, Control of etching behavior of Mn–Zn ferrite in a laser-chemical reaction by MeV ion beam modification . . . B59/60 (1991) 861
Lu, Z., see Jeong, H.-S. . . . B59/60 (1991) 1285
Lübke, K., see Palmetshofer, L. . . . B59/60 (1991) 1081
Lucas, S., see Terwagne, G. . . . B59/60 (1991) 93
Lucas, S., G. Terwagne, M. Piette and F. Bodart, Study of nitrogen distributions implanted at high temperature into aluminum . . . B59/60 (1991) 925
Lui Guifu , see Yu Zengliang . . . B59/60 (1991) 705
Luo Yan, see Zhang Tonghe . . . B59/60 (1991) 1098

Ma, K.B., see Yu, N. . . . B59/60 (1991) 1409
MacDonald, R.J., see King, B.V. . . . B59/60 (1991) 550
Machida, K., see Yamada, I. . . . B59/60 (1991) 216
Machida, O., J. Nagata, N. Noto and K. Mori, Effect of hydrogen ion bombardment on the characteristics of TiC films formed by the ion beam sputtering method . . . B59/60 (1991) 798
Machida, R., see Yamada, I. . . . B59/60 (1991) 219
Maclennan, C.G., see Benit, J. . . . B59/60 (1991) 68
Maex, K., G. Brijs, J. Vanhellemont and W. Vandervorst, Formation of thin films of monocrystalline $CoSi_2$ on (100) Si . . . B59/60 (1991) 660
Maex, K., see Vantomme, A. . . . B59/60 (1991) 680
Maex, K., see White, A.E. . . . B59/60 (1991) 693
Maeyama, Y., see Yamada, I. . . . B59/60 (1991) 216
Magruder, R.H., see Becker, K. . . . B59/60 (1991) 1304
Magruder III, R.H., R.A. Zuhr and R.A. Weeks, Dose rate dependence of the optical absorption of Cu implanted silica . . . B59/60 (1991) 1308
Malone, D., see Hummel, R.E. . . . B59/60 (1991) 297
Manabe, T., see Inoue, N. . . . B59/60 (1991) 1328
Manory, R.R., see Nath, V.C. . . . B59/60 (1991) 946
Mantl, S., see Fichtner, P.F.P. . . . B59/60 (1991) 632
Mantl, S., R. Jebasinski and D. Hartmann, The effect of dose on the growth of buried $CoSi_2$ layers in (111) and (100) Si produced by ion implantation . . . B59/60 (1991) 666
Mantl, S., see Li, J. . . . B59/60 (1991) 989
Mantl, S., see Holländer, B. . . . B59/60 (1991) 994
Marest, G., see Tosello, C. . . . B59/60 (1991) 545

Marest, G., see El Khakani, M.A. . . . B59/60 (1991) 817
Marest, G. and M.A. El Khakani, ^{64}Ni implantation in ^{57}Fe thin films studied by RBS and CEMS techniques . B59/60 (1991) 833
Marest, G., see Donnet, C. . . . B59/60 (1991) 1177
Marest, G., see Donnet, C. . . . B59/60 (1991) 1205
Marton, D., see Gordon, J.S. . . . B59/60 (1991) 312
Maruo, T., see Tanaka, T. . . . B59/60 (1991) 116
Masaki, S., H. Kobayashi and H. Morisaki, Ion-beam-assisted deposition of Al films with strong preferential orientation . . . B59/60 (1991) 292
Massouras, G., see Romana, L. . . . B59/60 (1991) 567
Masuta, H., see Nakane, Y. . . . B59/60 (1991) 264
Mathevet, J.-P., A. Traverse and S. Megtert, High energy ion beam mixing of ceramic–metal multilayers: $La(OH)_3/Sr(OH)_2/Cu$ . . . B59/60 (1991) 1435
Matsumae, T., see Miyano, T. . . . B59/60 (1991) 1167
Matsumoto, Y., see Ueno, K. . . . B59/60 (1991) 1263
Matsumura, A., see Yoshida, Y. . . . B59/60 (1991) 962
Matsunami, N. and K. Kitoh, High-resolution measurements of ion energy loss in thin films . . . B59/60 (1991) 5
Matthews, A.P., M. Iwaki, Y. Horino, M. Satou and K. Yabe, Investigation of the effects of room-temperature nitrogen implantation on the precipitation of aluminium nitride . . . B59/60 (1991) 671
Mayer, D.C., see Knudsen, J.F. . . . B59/60 (1991) 1067
Mayer, J.W., see Alford, T.L. . . . B59/60 (1991) 401
Mayer, J.W., see Li, J. . . . B59/60 (1991) 989
Mayer, J.W., see Norton, M. G. . . . B59/60 (1991) 1215
McCafferty, E., see Natishan, P.M. . . . B59/60 (1991) 841
McCallum, J.C., see McHargue, C.J. . . . B59/60 (1991) 1362
McCallum, J.C., see Sklad, P.S. . . . B59/60 (1991) 1187
McCooeye, D.P., see Howe, L.M. . . . B59/60 (1991) 884
McCormick, A.W., see Wu, R.L.C. . . . B59/60 (1991) 1232
McCracken, G.M., see Zhu, J. . . . B59/60 (1991) 168
McEachern, R.L., see Brown, W.L. . . . B59/60 (1991) 182
McHargue, C.J., A. Perez and J.C. McCallum, The chemical state of iron ions implanted into silicon carbide . . B59/60 (1991) 1362
McHargue, C.J., see Sklad, P.S. . . . B59/60 (1991) 1187
Meftah, A., N. Merrien, N. Nguyen, F. Studer, H. Pascard and M. Toulemonde, High-energy irradiation of magnetic insulators by lead ions: appearance of a plateau in the damage efficiency . . . B59/60 (1991) 605
Megtert, S., see Mathevet, J.-P. . . . B59/60 (1991) 1435
Melo, A.A., see Soares, J.C. . . . B59/60 (1991) 1090
Mendenhall, M., see Derryberry, S.L. . . . B59/60 (1991) 1320
Mendenhall, M.H., see Weller, M.R. . . . B59/60 (1991) 102
Mendenhall, M.H. and R.A. Weller, High-resolution medium-energy backscattering spectrometry . . . B59/60 (1991) 120
Mendez, J., see Villechaise, P. . . . B59/60 (1991) 837
Merrien, N., see Meftah, A. . . . B59/60 (1991) 605
Meshii, M., see Koike, J. . . . B59/60 (1991) 471
Meyer, O., see Linker, G. . . . B59/60 (1991) 1458
Miehle, W., A. Plewnia and P. Ziemann, Amorphization of crystalline $AuIn_2$ films by low-temperature ion irradiation . . . B59/60 (1991) 410
Mikami, T., see Andoh, Y. . . . B59/60 (1991) 276
Mimault, J., see Rivière, J.P. . . . B59/60 (1991) 781
Min, Z., W.-Z. Li and H.-D. Li, Formation of transition metal carbide thin films by dual ion beam deposition at room temperature . . . B59/60 (1991) 1358
Miotello, A., see Kelly, R. . . . B59/60 (1991) 517
Miotello, A., see Gratton, L.M. . . . B59/60 (1991) 541
Miyano, T., T. Matsumae, H. Yoko-o, Y. Andoh, M. Kiuchi and M. Satou, Effect of high energy ion implantation on sapphire . . . B59/60 (1991) 1167
Miyazaki, T., see Nakane, Y. . . . B59/60 (1991) 264
Mohite, S.S., see Bridwell, L.B. . . . B59/60 (1991) 1240
Moncoffre, N., see El Khakani, M.A. . . . B59/60 (1991) 817
Moncoffre, N., A comparison between ion implantation into sapphire and polycrystalline alumina . . . B59/60 (1991) 1129
Moncoffre, N., see Donnet, C. . . . B59/60 (1991) 1177
Moncoffre, N., see Donnet, C. . . . B59/60 (1991) 1205
Moore, F.G. and H.B. Dietrich, Dose-rate dependent electrical activation of silicon and sulphur implanted into GaAs . . . B59/60 (1991) 978
Moore, F.G., P.B. Klein and H.B. Dietrich, Type conversion of epitaxial GaAs layers after heavy ion MeV implantation and annealing . . . B59/60 (1991) 1103

Moore, J.L., see Golanski, A. . . . B59/60 (1991) 444
Mordkovich, V.N., see Danilin, A.B. . . . B59/60 (1991) 985
Moretti, P., P. Thevenard, F.R. Sommerfeld and G. Godefroy, Ion implantation effects in $BaTiO_3$ single crystals B59/60 (1991) 1228
Mori, H., see Kanno, I. . . . B59/60 (1991) 920
Mori, K., see Machida, O. . . . B59/60 (1991) 798
Morisaki, H., see Masaki, S. . . . B59/60 (1991) 292
Morishita, T., see Yoshida, I. . . . B59/60 (1991) 1443
Morse, D.H., see Antolak, A.J. . . . B59/60 (1991) 13
Moss, M.G., see Giedd, R.E. . . . B59/60 (1991) 1253
Motonami, Y., see Yoshida, Y. . . . B59/60 (1991) 962
Mount, C.K., see Ferber, H. . . . B59/60 (1991) 957
Msaad, H., see Børgesen, P. . . . B59/60 (1991) 563
Munir, Z.A., see Brown, D.W. . . . B59/60 (1991) 627
Musket, R.G., see Brown, D.W. . . . B59/60 (1991) 627
Myers, S.M., see Bourcier, R.J. . . . B59/60 (1991) 905
Myers, S.M., see Follstaedt, D.M. . . . B59/60 (1991) 909

Nagai, S., Surface chemical reactions of Al induced by low-energy D_2^+, N_2^+, CO^+, and CO_2^+ ion bombardment . . . B59/60 (1991) 936
Nagano, J., see Yamazaki, H. . . . B59/60 (1991) 981
Nagase, Y., see Yamada, I. . . . B59/60 (1991) 219
Nagata, J., see Machida, O. . . . B59/60 (1991) 798
Nagata, S., see Takahiro, K. . . . B59/60 (1991) 1374
Nakagawa, S.T., Z-dependence of low-energy electronic stopping . . . B59/60 (1991) 18
Nakane, Y., H. Masuta, Y. Honda, F. Fujimoto, T. Miyazaki and S. Yano, Formation of indium–tin oxide (ITO) films by the dynamic mixing method . . . B59/60 (1991) 264
Nakashima, S., see Chayahara, A. . . . B59/60 (1991) 893
Namba, S., see Gamo, K. . . . B59/60 (1991) 190
Namba, S., see Sanda, H. . . . B59/60 (1991) 778
Namba, S., see Lu, Y.F. . . . B59/60 (1991) 861
Namba, S., see Sayama, H. . . . B59/60 (1991) 1094
Namba, S., see Takai, M. . . . B59/60 (1991) 1120
Namba, Y., see Yamada, I. . . . B59/60 (1991) 216
Narsale, A.M., see Salvi, V.P. . . . B59/60 (1991) 1124
Narusawa, T., see Kubo, M. . . . B59/60 (1991) 332
Nastasi, M., J.-P. Hirvonen, T.G. Zocco and T.R. Jervis, Microstructure and tribology of ion-mixed Fe/Ti/C multilayers on AISI 304 stainless steel . . . B59/60 (1991) 806
Nastasi, M., see Kramer, K.M. . . . B59/60 (1991) 865
Nastasi, M., see Bordes, N. . . . B59/60 (1991) 1399
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Natishan, P.M., E. McCafferty and G.K. Hubler, The pitting corrosion behavior of aluminum ion implanted with tantalum . . . B59/60 (1991) 841
Nawathey-Dikshit, R., see Ogale, S.B. . . . B59/60 (1991) 1350
Nender, C., see Biersack, J.P. . . . B59/60 (1991) 21
Nguyen, N., see Meftah, A. . . . B59/60 (1991) 605
Niedrig, H., see Rübesame, D. . . . B59/60 (1991) 80
Niedrig, H., see Knapp, H. . . . B59/60 (1991) 131
Niedrig, H., see Hanke, R. . . . B59/60 (1991) 135
Niehof, A., S. Renner, Ch. Buchal and W. Heiland, Optical channel waveguides produced with high-dose Ti^+ implantation . . . B59/60 (1991) 1355
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Niewöhner, L. and D. Depta, Formation of $CoSi_2$ by ion beam mixing and rapid thermal annealing . . . B59/60 (1991) 523
Nishi, Y., see Inoue, N. . . . B59/60 (1991) 1328
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Nishijima, S., see Kanno, I. . . . B59/60 (1991) 920
Nishimiya, N., see Ueno, K. . . . B59/60 (1991) 1263

Nishimiya, N., K. Ueno, M. Noshiro and M. Satou, Chemical processes and surface hardening in ion-implanted polyester films . . . B59/60 (1991) 1276
Nishimura, O., see Fukui, Y. . . . B59/60 (1991) 812
Nishiura, T., see Kanno, I. . . . B59/60 (1991) 920
Nishiyama, F., see Takahiro, K. . . . B59/60 (1991) 9
Nishiyama, F., see Takahiro, K. . . . B59/60 (1991) 1374
Nishiyama, S., see Andoh, Y. . . . B59/60 (1991) 276
Nomoto, K., see Kanno, I. . . . B59/60 (1991) 920
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Noshiro, M., see Ueno, K. . . . B59/60 (1991) 1263
Noshiro, M., see Nishimiya, N. . . . B59/60 (1991) 1276
Noto, N., see Machida, O. . . . B59/60 (1991) 798
Novak, S., see Park, C. . . . B59/60 (1991) 159

Obara, K., Electron attachment to niobium clusters and the condensation process . . . B59/60 (1991) 211
Öchsner, R., A. Kluge, L. Frey and H. Ryssel, Tribological properties of carbonized photoresist . . . B59/60 (1991) 793
Oechsner, R., see Kobs, K. . . . B59/60 (1991) 746
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Ogale, S.B., see Viswanathan, R. . . . B59/60 (1991) 1439
Ogata, K., Y. Andoh, S. Sakai, M. Sone and F. Fujimoto, Charging effects and ultraviolet irradiation for carbon films prepared by ion beam bombardment . . . B59/60 (1991) 225
Ogata, K., Y. Andoh, S. Sakai and F. Fujimoto, Crystalline orientation control for aluminum nitride films prepared by ion-beam-assisted technology . . . B59/60 (1991) 229
Ogata, K., see Andoh, Y. . . . B59/60 (1991) 276
Ogata, K., see Sakai, S. . . . B59/60 (1991) 288
Oguri, K., see Nishi, Y. . . . B59/60 (1991) 1418
Ohta, K., J. Sakano and S. Furukawa, Formation of a high-crystalline-quality SiGeB layer by Ge and B co-implantation . . . B59/60 (1991) 1113
Ohtani, F., see Kobayashi, N. . . . B59/60 (1991) 449
Ohyu, K., see Tamura, M. . . . B59/60 (1991) 572
Okada, T., see Kanno, I. . . . B59/60 (1991) 920
Okamoto, P.R., see Koike, J. . . . B59/60 (1991) 471
Orrman-Rossiter, K.G., A.H. Al-Bayati, D.G. Armour, S.E. Donnelly and J.A. van den Berg, Ion beam deposited epitaxial thin silicon films . . . B59/60 (1991) 197
Osaka, Y., see Takahiro, K. . . . B59/60 (1991) 9
Osaka, Y., see Takahiro, K. . . . B59/60 (1991) 1374
Ottaviani, G., see Valeri, S. . . . B59/60 (1991) 98
Oxorn, K., see Touhouche, K. . . . B59/60 (1991) 676
Oyoshi, K., T. Tagami, K. Yamashita and S. Tanaka, Formation of phosphosilicate glass layers in glasses by ion implantation . . . B59/60 (1991) 1324
Ozturk, O., see Wei, R. . . . B59/60 (1991) 731
Ozturk, O., see Williamson, D.L. . . . B59/60 (1991) 737
Ozzello, A., see Grummon, D.S. . . . B59/60 (1991) 1271

Padmanabhan, K.R., see Auner, G.W. . . . B59/60 (1991) 504
Padmanabhan, K.R., see Cheng, Y.-T. . . . B59/60 (1991) 509
Palmetshofer, L., J. Kastner and K. Lübke, Electrical activation and defects in silicon-implanted and rapidly thermal-annealed gallium arsenide . . . B59/60 (1991) 1081
Pan, F., see Pan, X.Z. . . . B59/60 (1991) 233
Pan, X.-Z., see Li, J.-C. . . . B59/60 (1991) 1110
Pan, X.Z., Z.L. Zhu, F. Pan, Y.Z. Yang, H.Z. Huang and T. Yu, Effects of ion energy on microstructure and properties of IAD metal films . . . B59/60 (1991) 233
Pappert, S.A., see Xia, W. . . . B59/60 (1991) 491
Parellada, J., see Tosello, C. . . . B59/60 (1991) 545
Parikh, N., see Yu, N. . . . B59/60 (1991) 1061
Parikh, N.R., see Sandhu, G.S. . . . B59/60 (1991) 145
Park, C., see Klein, K.M. . . . B59/60 (1991) 60
Park, C., K.M. Klein, A.F. Tasch, R.B. Simonton, D.E. Kamenitsa and S. Novak, Boron implant profile variation across a single wafer due to electrostatic scanning . . . B59/60 (1991) 159
Park, J.L., see Golanski, A. . . . B59/60 (1991) 444

Pascard, H., see Meftah, A. . . . B59/60 (1991) 605
Pascual, R., see Clapham, L. . . . B59/60 (1991) 1404
Paszti, F., see Nielsen, B.R. . . . B59/60 (1991) 772
Pászti, F., see Feuser, U. . . . B59/60 (1991) 1049
Patnaik, B., see Yu, N. . . . B59/60 (1991) 1061
Patnaik, B.K., see Sandhu, G.S. . . . B59/60 (1991) 145
Pearton, S.J., Ion implantation doping and isolation of III–V semiconductors . . . B59/60 (1991) 970
Pearton, S.J., U.K. Chakrabarti, W.S. Hobson, C. Constantine and D. Johnson, Low damage dry etching of III–V compound semiconductors using electron cyclotron resonance discharges . . . B59/60 (1991) 1015
Pedraza, D.F., see Allen, W.R. . . . B59/60 (1991) 1159
Pedraza, D.F., see Chen, Y. . . . B59/60 (1991) 1163
Pedraza, D.F., see Caro, J.A. . . . B59/60 (1991) 880
Pennycook, S.J., see Golanski, A. . . . B59/60 (1991) 444
Perez, A., see McHargue, C.J. . . . B59/60 (1991) 1362
Perez, A., see Abonneau, E. . . . B59/60 (1991) 1183
Peternelj, J., see Jenčič, I. . . . B59/60 (1991) 458
Peterson, D.L., see Braunstein, G. . . . B59/60 (1991) 1032
Phillips, D., see Howe, L.M. . . . B59/60 (1991) 884
Pichler, P., see Schork, R. . . . B59/60 (1991) 499
Piette, M., see Lucas, S. . . . B59/60 (1991) 925
Pitaval, M., see Nielsen, B.R. . . . B59/60 (1991) 772
Plewnia, A., see Miehle, W. . . . B59/60 (1991) 410
Poate, J.M., see Roorda, S. . . . B59/60 (1991) 344
Poate, J.M., see White, A.E. . . . B59/60 (1991) 693
Poate, J.M., see Polman, A. . . . B59/60 (1991) 1313
Poker, D.B., see Golanski, A. . . . B59/60 (1991) 444
Poker, D.B., see Xia, W. . . . B59/60 (1991) 491
Politiek, J., see Kobs, K. . . . B59/60 (1991) 746
Polman, A., see Roorda, S. . . . B59/60 (1991) 344
Polman, A., D.C. Jacobson, A. Lidgard, J.M. Poate and G.W. Arnold, Photoluminescence and structural characterization of MeV erbium-implanted silica glass . . . B59/60 (1991) 1313
Pontau, A.E., see Antolak, A.J. . . . B59/60 (1991) 13
Pope, L.E., see Knapp, J.A. . . . B59/60 (1991) 742
Prazak, M., see Cerny, F. . . . B59/60 (1991) 762
Prieler, M., see Dietz, V. . . . B59/60 (1991) 284
Prikhodko, I.I., see Goltsev, V.P. . . . B59/60 (1991) 558
Principi, G., see Gratton, L.M. . . . B59/60 (1991) 541
Principi, G., see Tosello, C. . . . B59/60 (1991) 545
Prinja, A.K. and L.W. Brasure, Transport theory modeling of atomic collisions in mixtures . . . B59/60 (1991) 46
Prins, J.F., see Spits, R.A. . . . B59/60 (1991) 1366
Prins, J.F., Annealing effects when activating dopant atoms in ion-implanted diamond layers . . . B59/60 (1991) 1387
Priolo, F., see Spinella, C. . . . B59/60 (1991) 363
Priolo, F., see Battaglia, A. . . . B59/60 (1991) 382
Procop, M., see Valeri, S. . . . B59/60 (1991) 98
Pronko, J.G., see Kellock, A.J. . . . B59/60 (1991) 249
Pronko, J.G., see Tin, C.C. . . . B59/60 (1991) 623
Pronko, P.P., see Wu, R.L.C. . . . B59/60 (1991) 1232
Puranik, S.G., see King, B.V. . . . B59/60 (1991) 550

Qin Dong, see Tan Hui . . . B59/60 (1991) 785
Qiu, X., R.A. Dodd, J.R. Conrad, A. Chen and F.J. Worzala, Microstructural study of nitrogen-implanted Ti–6Al–4V alloy . . . B59/60 (1991) 951
Qu Baochun, see Chen Yuanru . . . B59/60 (1991) 1295
Quintana, J., see Williams, J.M. . . . B59/60 (1991) 845

Rabalais, J.W., see Gordon, J.S. . . . B59/60 (1991) 312
Radermacher, K., see Fichtner, P.F.P. . . . B59/60 (1991) 632
Rahioui, A., see Donnet, C. . . . B59/60 (1991) 1205
Rai, A.K., R.S. Bhattacharya, C.S. Yust and C.E. DeVore, The microstructure and tribological properties of ion beam assisted Cd–O and Ti–O coatings . . . B59/60 (1991) 280
Rai, A.K., see Bhattacharya, R.S. . . . B59/60 (1991) 788
Raineri, V., see Schreutelkamp, R.J. . . . B59/60 (1991) 614

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Rainville, M.H., see Howe, L.M. . . . B59/60 (1991) 884
Rajershee, S.V., see Ogale, S.B. . . . B59/60 (1991) 1350
Ramabadran, U.B., H.E. Jackson and G.C. Farlow, High-dose implantation of Si in SiO_2: formation of Si crystallites after annealing . . . B59/60 (1991) 637
Ramlau, R., see Arnold, A. . . . B59/60 (1991) 726
Ramos, S.M.M., see Romana, L. . . . B59/60 (1991) 567
Ramos, S.M.M., B. Canut, L. Gea, L. Romana, J. Le Brusq, P. Thevenard and M. Brunel, Evidence of chemical effects in niobium implanted oxides . . . B59/60 (1991) 1201
Ramos, S.M.M., see Canut, B. . . . B59/60 (1991) 1211
Rangel, C.M., see Nielsen, B.R. . . . B59/60 (1991) 772
Rangwala, A.A., see Salvi, V.P. . . . B59/60 (1991) 1124
Rao, R.R., see Viswanathan, R. . . . B59/60 (1991) 1439
Rasulev, U.Kh., see Belykh, S.F. . . . B59/60 (1991) 106
Redina, I.V., see Belykh, S.F. . . . B59/60 (1991) 65
Redina, I.V., see Belykh, S.F. . . . B59/60 (1991) 72
Redina, I.V., see Belykh, S.F. . . . B59/60 (1991) 106
Rehn, L.E., see Alexander, D.E. . . . B59/60 (1991) 462
Rehn, L.E., see Koike, J. . . . B59/60 (1991) 471
Rehn, L.E., see Woo, J.J. . . . B59/60 (1991) 537
Rehn, L.E., see Lam, N.Q. . . . B59/60 (1991) 889
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Remmel, J., see Linker, G. . . . B59/60 (1991) 1458
Renner, S., see Niehof, A. . . . B59/60 (1991) 1355
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Ridgway, M.C., S.T. Johnson and R.G. Elliman, Ion-beam induced epitaxial crystallization of III–V compound semiconductors . . . B59/60 (1991) 454
Rimini, E., see Spinella, C. . . . B59/60 (1991) 363
Rimini, E., see Battaglia, A. . . . B59/60 (1991) 382
Rivière, J.P., Ph. Guesdon and J. Delafond, Structure and properties of TiB_2 coatings produced by dynamic ion mixing . . . B59/60 (1991) 237
Rivière, J.P., see Jaouen, C. . . . B59/60 (1991) 406
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Rivière, J.P., see Villechaise, P. . . . B59/60 (1991) 837
Robertson, D.E., see Giedd, R.E. . . . B59/60 (1991) 1253
Robertson, I.M., see Bench, M.W. . . . B59/60 (1991) 372
Robertson, I.M., see Jenčič, I. . . . B59/60 (1991) 458
Rollett, A.D., see Bordes, N. . . . B59/60 (1991) 1399
Romana, L., G. Fuchs, M. Brunel, G. Massouras, B. Canut, R. Brenier, S.M.M. Ramos and P. Thevenard, High resolution microscopy study of niobium–sapphire interfaces modified by ion beam mixing . . . B59/60 (1991) 567
Romana, L., see Ramos, S.M.M. . . . B59/60 (1991) 1201
Romana, L., see Sklad, P.S. . . . B59/60 (1991) 1187
Romary, H., see Bedell, C.J. . . . B59/60 (1991) 245
Romary, J-M., see Bedell, C.J. . . . B59/60 (1991) 245
Rong, T.W., see Lin, S.H. . . . B59/60 (1991) 1257
Roorda, S., J.S. Custer, W.C. Sinke, J.M. Poate, D.C. Jacobson, A. Polman and F. Spaepen, Structural relaxation in amorphous silicon and the role of network defects . . . B59/60 (1991) 344
Rossi, M., see Vitali, G. . . . B59/60 (1991) 1077
Rou, S.H., see Soble II, C.N. . . . B59/60 (1991) 155
Rübesame, D., M. Sternberg, T. Guerlin and H. Niedrig, Investigation of angular distributions of ion-induced atomic emission produced under various ion incidence angles . . . B59/60 (1991) 80
Rübesame, D., see Knapp, H. . . . B59/60 (1991) 131
Rübesame, D., see Hanke, R. . . . B59/60 (1991) 135
Rubio, J.D., see Hart, R.R. . . . B59/60 (1991) 427
Ryabchikov, A.I., N.M. Arsubov, N.A. Vasilyiev and S.V. Dektyarev, The Raduga multipurpose ion/plasma source for surface modification of construction materials . . . B59/60 (1991) 124
Ryssel, H., see Schork, R. . . . B59/60 (1991) 499
Ryssel, H., see Ye, M. . . . B59/60 (1991) 528

Ryssel, H., see Langguth, K. . . . B59/60 (1991) 718
Ryssel, H., see Kobs, K. . . . B59/60 (1991) 746
Ryssel, H., see Öchsner, R. . . . B59/60 (1991) 793
Ryssel, H., see Sayama, H. . . . B59/60 (1991) 1094
Ryssel, H., see Takai, M. . . . B59/60 (1991) 1120

Sadahiro, T., see Yoshida, Y. . . . B59/60 (1991) 962
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Sakai, S., see Ogata, K. . . . B59/60 (1991) 225
Sakai, S., see Ogata, K. . . . B59/60 (1991) 229
Sakai, S., K. Ogata and Y. Andoh, Crystal structure of aluminum films prepared by ion beam assisted technology B59/60 (1991) 288
Sakamoto, I., see Hayashi, N. . . . B59/60 (1991) 897
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Sanda, H., see Lu, Y.F. . . . B59/60 (1991) 861
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Sant, S., see Lau, W.M. . . . B59/60 (1991) 316
Sarholt-Kristensen, L., A. Johansen, E. Johnson, S. Steenstrup, N. Chechenin and V.S. Chernysh, Sputtering of copper crystals by soluble and nonsoluble ions . . . B59/60 (1991) 85
Saris, F.W., see Schreutelkamp, R.J. . . . B59/60 (1991) 614
Saris, F.W., see Raineri, V. . . . B59/60 (1991) 1056
Sartwell, B.D., see Kant, R.A. . . . B59/60 (1991) 89
Sasaki, T., see Chayahara, A. . . . B59/60 (1991) 893
Satho, M., see Yokota, K. . . . B59/60 (1991) 1431
Sato, K., see Kawagoe, Y. . . . B59/60 (1991) 1426
Sato, M., see Yoshida, Y. . . . B59/60 (1991) 962
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Satoh, F., see Yamada, I. . . . B59/60 (1991) 216
Satoh, H., see Sugizaki, Y. . . . B59/60 (1991) 722
Satou, M., see Horino, Y. . . . B59/60 (1991) 139
Satou, M., see Ensinger, W. . . . B59/60 (1991) 259
Satou, M., see Matthews, A.P. . . . B59/60 (1991) 671
Satou, M., see Sanda, H. . . . B59/60 (1991) 778
Satou, M., see Lu, Y.F. . . . B59/60 (1991) 861
Satou, M., see Chayahara, A. . . . B59/60 (1991) 893
Satou, M., see Miyano, T. . . . B59/60 (1991) 1167
Satou, M., see Ueno, K. . . . B59/60 (1991) 1263
Satou, M., see Nishimiya, N. . . . B59/60 (1991) 1276
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Schalek, R., see Grummon, D.S. . . . B59/60 (1991) 1271
Schilling, W., see Dietz, V. . . . B59/60 (1991) 284
Schilling, W., see Hardtke, Ch. . . . B59/60 (1991) 377
Schmidt, V.H., see Saleh, A.A. . . . B59/60 (1991) 1372
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Schreutelkamp, R.J., see Raineri, V. . . . B59/60 (1991) 1056
Schröer, A., see Liu Xianghuai . . . B59/60 (1991) 851
Schwarz, S.A., see Xia, W. . . . B59/60 (1991) 491
Sealy, B.J., see Soares, J.C. . . . B59/60 (1991) 1090
Seijbel, L.J., see Huijgen, T.P. . . . B59/60 (1991) 150

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Sekiguchi, A., see Fujihana, T. . . . B59/60 (1991) 764
Sekiguchi, H., see Ito, K. . . . B59/60 (1991) 321
Sellschop, J.P.F., see Spits, R.A. . . . B59/60 (1991) 1366
Sharma, R.P., see Rehn, L.E. . . . B59/60 (1991) 1463
Sheng, K.L., see Lin, S.H. . . . B59/60 (1991) 1257
Shen Jinghua, see Zhang Tonghe . . . B59/60 (1991) 828
Shibata, M., see Nishi, Y. . . . B59/60 (1991) 1418
Shigematu, H., see Sanda, H. . . . B59/60 (1991) 778
Shima, T., see Inoue, N. . . . B59/60 (1991) 1328
Shima, T., see Nishi, Y. . . . B59/60 (1991) 1415
Shima, T., see Nishi, Y. . . . B59/60 (1991) 1418
Shimizu, G., see Nishi, Y. . . . B59/60 (1991) 1418
Shimizu, S., see Yoshida, Y. . . . B59/60 (1991) 962
Shinohara, M., see Kobayashi, N. . . . B59/60 (1991) 449
Short, K.T., see White, A.E. . . . B59/60 (1991) 693
Shutthanandan, V., see Saleh, A.A. . . . B59/60 (1991) 1372
Simonton, R.B., see Park, C. . . . B59/60 (1991) 159
Simplicio, M.H., see Nielsen, B.R. . . . B59/60 (1991) 772
Sinke, W.C., see Roorda, S. . . . B59/60 (1991) 344
Sinopoli, L., see Costantini, J.M. . . . B59/60 (1991) 600
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Smith, R.J., see Lee, R.Y. . . . B59/60 (1991) 532
Smith, R.J., see Kim, H.K. . . . B59/60 (1991) 554
Smith, R.J., see Saleh, A.A. . . . B59/60 (1991) 1372
Smithey, R., see Linker, G. . . . B59/60 (1991) 1458
Soares, J.C., see Nielsen, B.R. . . . B59/60 (1991) 772
Soares, J.C., see Feuser, U. . . . B59/60 (1991) 1049
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Sommerfeld, F.R., see Moretti, P. . . . B59/60 (1991) 1228
Sone, M., see Ogata, K. . . . B59/60 (1991) 225
Song, J.H., see Lee, R.Y. . . . B59/60 (1991) 532
Song, J.H., see Kim, H.K. . . . B59/60 (1991) 554
Sood, D.K., see Nath, V.C. . . . B59/60 (1991) 946
Sood, D.K., see Zhou, W. . . . B59/60 (1991) 1195
Sorensen, N.R., see Knapp, J.A. . . . B59/60 (1991) 742
Sorensen, N.R., see Demaree, J.D. . . . B59/60 (1991) 757
Sosnowski, M., see Brown, W.L. . . . B59/60 (1991) 182
Soukieh, M., see Goltsev, V.P. . . . B59/60 (1991) 823
Spaepen, F., see Roorda, S. . . . B59/60 (1991) 344
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Spohr, R., see Audouard, A. . . . B59/60 (1991) 414
Stas, V.F., see Gerasimenko, N.N. . . . B59/60 (1991) 647
Steenstrup, S., see Sarholt-Kristensen, L. . . . B59/60 (1991) 85
Stein, H.J., Formation and stability of As–H bonds in H-implanted GaAs . . . B59/60 (1991) 1106
Sternberg, M., see Rübesame, D. . . . B59/60 (1991) 80
Strack, H., see Kallweit, R. . . . B59/60 (1991) 1288
Strehlau, B., see Linker, G. . . . B59/60 (1991) 1458
Stringer, J., see Hou, P.Y. . . . B59/60 (1991) 1345
Stritzker, B., see Holländer, B. . . . B59/60 (1991) 994
Stubbins, J.F., see Yacout, A.M. . . . B59/60 (1991) 57
Stubbins, J.F., see Lam, N.Q. . . . B59/60 (1991) 889
Studer, F., see Meftah, A. . . . B59/60 (1991) 605

Suchanek, J., see Cerny, F. . . . B59/60 (1991) 762
Suegara, M., see Nishi, Y. . . . B59/60 (1991) 1422
Suganomata, S., see Saito, Y. . . . B59/60 (1991) 1173
Sugiyama, H., see Yamada, I. . . . B59/60 (1991) 219
Sugizaki, Y., T. Furuya and H. Satoh, Influence of nitrogen implantation on the hydrogen absorption by titanium B59/60 (1991) 722
Sun Guiru, see Zhang Tonghe . . . B59/60 (1991) 828
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Suzuki, K., see Yoshida, I. . . . B59/60 (1991) 1443
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Swanson, M.L., see Sandhu, G.S. . . . B59/60 (1991) 145
Szilagyi, E., see Feuser, U. . . . B59/60 (1991) 1049

Tagami, T., see Oyoshi, K. . . . B59/60 (1991) 1324
Takagi, S., see Nishi, Y. . . . B59/60 (1991) 1415
Takagi, S., see Nishi, Y. . . . B59/60 (1991) 1418
Takagi, S., see Nishi, Y. . . . B59/60 (1991) 1422
Takahashi, K., see Fujihana, T. . . . B59/60 (1991) 764
Takahashi, K., see Sato, S. . . . B59/60 (1991) 1391
Takahashi, M., see Kikkawa, S. . . . B59/60 (1991) 341
Takahashi, Y., see Nishi, Y. . . . B59/60 (1991) 1415
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Takai, M., see Sanda, H. . . . B59/60 (1991) 778
Takai, M., see Lu, Y.F. . . . B59/60 (1991) 861
Takai, M., see Sayama, H. . . . B59/60 (1991) 1094
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Takaoka, G., see Brown, W.L. . . . B59/60 (1991) 182
Takaoka, G.H., see Hirayama, H. . . . B59/60 (1991) 207
Takaoka, G.H., see Yamada, I. . . . B59/60 (1991) 216
Tamura, M., T. Ando and K. Ohyu, MeV-ion-induced damage in Si and its annealing . . . B59/60 (1991) 572
Tan, T.Y., see Lee, S.-T. . . . B59/60 (1991) 999
Tanaka, M., see Kawagoe, Y. . . . B59/60 (1991) 1426
Tanaka, S., see Yamada, I. . . . B59/60 (1991) 302
Tanaka, S., see Zuhr, R.A. . . . B59/60 (1991) 308
Tanaka, S., see Oyoshi, K. . . . B59/60 (1991) 1324
Tanaka, S., see Yoshida, I. . . . B59/60 (1991) 1443
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Tang, S., see Lam, N.Q. . . . B59/60 (1991) 889
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Taniguchi, S., see Liu Xianghuai . . . B59/60 (1991) 851
Tanoue, H., see Sakamoto, I. . . . B59/60 (1991) 900
Tao, Y., see Touhouche, K. . . . B59/60 (1991) 676
Tao Mingde, see Tan Hui . . . B59/60 (1991) 785
Tasch, A.F., see Klein, K.M. . . . B59/60 (1991) 60
Tasch, A.F., see Park, C. . . . B59/60 (1991) 159
Te Kaat, E.H., see Lindner, J.K.N. . . . B59/60 (1991) 655
Te Kaat, E.H., see Arnold, A. . . . B59/60 (1991) 726
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Terwagne, G., see Lucas, S. . . . B59/60 (1991) 925
Tesmer, J.R., see Kramer, K.M. . . . B59/60 (1991) 865
Theirich, D. and J. Engemann, Influence of reflected primary ions and nonunity sticking coefficients on film stoichiometry during ion-beam-sputter deposition of multicomponent targets . . . B59/60 (1991) 336
Thevenard, P., see Romana, L. . . . B59/60 (1991) 567
Thevenard, P., see Nielsen, B.R. . . . B59/60 (1991) 772

Thevenard, P., see Ramos, S.M.M. . . . B59/60 (1991) 1201
Thevenard, P., see Canut, B. . . . B59/60 (1991) 1211
Thevenard, P., see Moretti, P. . . . B59/60 (1991) 1228
Thevenard, P., see Davenas, J. . . . B59/60 (1991) 1249
Thijsse, B.J., see Huijgen, T.P. . . . B59/60 (1991) 150
Thijsse, B.J., see Seijbel, L.J. . . . B59/60 (1991) 1336
Thijsse, B.J., see Hoondert, W.H.B. . . . B59/60 (1991) 1340
Thomé, L., see Audouard, A. . . . B59/60 (1991) 414
Thomé, L., see Benyagoub, A. . . . B59/60 (1991) 418
Thompson, P.E., MeV ion implantation in GaAs technology . . . B59/60 (1991) 592
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Tolk, N.H., see Wang, P.W. . . . B59/60 (1991) 1317
Tomasi, A., see Gratton, L.M. . . . B59/60 (1991) 541
Torp, B., see Nielsen, B.R. . . . B59/60 (1991) 772
Tosello, C., see Gratton, L.M. . . . B59/60 (1991) 541
Tosello, C., L.M. Gratton, W. Keune, R.A. Brand, S. Lo Russo, J. Parellada, J.M. Fernandez, G. Marest, M.A. El Khakani, G. Principi and A. Gupta, Irradiation effects at the Ni/Fe interface . . . B59/60 (1991) 545
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Tousset, J., see El Khakani, M.A. . . . B59/60 (1991) 817
Tousset, J., see Donnet, C. . . . B59/60 (1991) 1177
Tousset, J., see Donnet, C. . . . B59/60 (1991) 1205
Townsend, P.D., see Zhang, L. . . . B59/60 (1991) 1147
Townsend, P.D., see Babsail, L. . . . B59/60 (1991) 1219
Townsend, P.D., see Chandler, P.J. . . . B59/60 (1991) 1223
Townsend, P.D., see Wood, R.A. . . . B59/60 (1991) 1331
Traverse, A., see Mathevet, J.-P. . . . B59/60 (1991) 1435
Treglio, J.R., see Williams, J.M. . . . B59/60 (1991) 845
Treilleux, M., see Abonneau, E. . . . B59/60 (1991) 1183
Trudeau, Y., see Touhouche, K. . . . B59/60 (1991) 676
Trudeau, Y.B., G.E. Kajrys, G. Gagnon and J.L. Brebner, Damage induced in GaAs by high-energy Be, Si and Se implantation . . . B59/60 (1991) 609
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Ueno, K., see Nishimiya, N. . . . B59/60 (1991) 1276
Uglov, V.V., see Goltsev, V.P. . . . B59/60 (1991) 558
Uglov, V.V., see Goltsev, V.P. . . . B59/60 (1991) 751
Uglov, V.V., see Goltsev, V.P. . . . B59/60 (1991) 823
Uglov, V.V., see Goltsev, V.P. . . . B59/60 (1991) 930
Ullmaier, H., see Hardtke, Ch. . . . B59/60 (1991) 377
Usui, H., see Brown, W.L. . . . B59/60 (1991) 182
Usui, H., see Hirayama, H. . . . B59/60 (1991) 207
Usui, H., see Yamada, I. . . . B59/60 (1991) 216
Usui, H., see Yamada, I. . . . B59/60 (1991) 219
Usui, H., see Yamada, I. . . . B59/60 (1991) 302
Usui, H., see Adachi, M. . . . B59/60 (1991) 940
Uzureau, J.L., see Costantini, J.M. . . . B59/60 (1991) 600

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Valeri, S., A. di Bona, G. Ottaviani and M. Procop, Ion beam effects on the surface and near-surface composition of $TaSi_2$ . . . B59/60 (1991) 98
Vallet, C.E. and C.W. White, Application of ion implantation to electrochemical studies . . . B59/60 (1991) 855
Van den Berg, J.A., see Orrman-Rossiter, K.G. . . . B59/60 (1991) 197
Van den Berg, J.A., see Gordon, J.S. . . . B59/60 (1991) 312
Van den Beukel, A., see Huijgen, T.P. . . . B59/60 (1991) 150
Van den Beukel, A., see Seijbel, L.J. . . . B59/60 (1991) 1336

Van den Beukel, A., see Hoondert, W.H.B. . . . B59/60 (1991) 1340
Van Veen, A., see Seijbel, L.J. . . . B59/60 (1991) 1336
Vancauwenberghe, O., see Herbots, N. . . . B59/60 (1991) 326
Vanderstraeten, H., see Vantomme, A. . . . B59/60 (1991) 680
Vandervorst, W., see Maex, K. . . . B59/60 (1991) 660
Vanhellemont, J., see Maex, K. . . . B59/60 (1991) 660
Vantomme, A., M.F. Wu, G. Langouche, K. Maex, H. Vanderstraeten and Y. Bruynseraede, Orientation and strain of single and double $CoSi_2$ epitaxial layers formed by ion implantation . . . B59/60 (1991) 680
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Vasil'yeva, T.N., see Fattakhov, Y.V. . . . B59/60 (1991) 1072
Vasilyiev, N.A., see Ryabchikov, A.I. . . . B59/60 (1991) 124
Venables, D. and K.S. Jones, Can recoil distribution models account for end-of-range damage? . . . B59/60 (1991) 1019
Venturini, E.L., see Barbour, J.C. . . . B59/60 (1991) 1395
Verucchi, R., see Valeri, S. . . . B59/60 (1991) 37
Vetter, J., see Audouard, A. . . . B59/60 (1991) 414
Vianden, R., see Feuser, U. . . . B59/60 (1991) 1049
Vidwans, S., see Salvi, V.P. . . . B59/60 (1991) 1124
Vijay, R.P., see Hart, R.R. . . . B59/60 (1991) 427
Villechaise, P., J. Mendez, P. Violan and J.P. Rivière, Influence of dynamical ion mixing of crystalline aluminium and nickel coatings on the fatigue behaviour of a 316L-type stainless steel . . . B59/60 (1991) 837
Vincenz, A.M., see Goktepe, O.F. . . . B59/60 (1991) 33
Violan, P., see Villechaise, P. . . . B59/60 (1991) 837
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Wada, S., see Yamada, I. . . . B59/60 (1991) 302
Wagner de Oliveira, R., see Behar, M. . . . B59/60 (1991) 1
Wan, H.H., see Lin, S.H. . . . B59/60 (1991) 1257
Wang, C.N., see Kim, H.K. . . . B59/60 (1991) 554
Wang, L.C., see Zhang, B.-X. . . . B59/60 (1991) 434
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Wang, W.Y., see Fan, W.D. . . . B59/60 (1991) 1086
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Wang Xuedong, see Yu Zengliang . . . B59/60 (1991) 705
Wang Yongqiang, see Bridwell, L.B. . . . B59/60 (1991) 1240
Was, G.S., see Alexander, D.E. . . . B59/60 (1991) 462
Was, G.S., see Demaree, J.D. . . . B59/60 (1991) 757
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Was, G.S., see Cavasin, D. . . . B59/60 (1991) 875
Watanabe, H., see Sato, S. . . . B59/60 (1991) 1391
Watanabe, K., see Yamazaki, H. . . . B59/60 (1991) 981
Webb, R.P., see Smith, R. . . . B59/60 (1991) 1378
Weeks, R.A., see Becker, K. . . . B59/60 (1991) 1304
Weeks, R.A., see Magruder III, R.H. . . . B59/60 (1991) 1308
Weeks, R.A., see Wang, P.W. . . . B59/60 (1991) 1317
Weeks, R.A., see Derryberry, S.L. . . . B59/60 (1991) 1320
Wege, S., see Hanke, R. . . . B59/60 (1991) 135

Wei, R., P.J. Wilbur, O. Ozturk and D.L. Williamson, Tribological studies of ultrahigh dose nitrogen-implanted iron and stainless steel . . . B59/60 (1991) 731
Wei, R., see Williamson, D.L. . . . B59/60 (1991) 737
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Weller, R.A., see Weller, M.R. . . . B59/60 (1991) 102
Weller, R.A., see Mendenhall, M.H. . . . B59/60 (1991) 120
Weller, R.A., see Derryberry, S.L. . . . B59/60 (1991) 1320
Whang, C.N., see Lee, R.Y. . . . B59/60 (1991) 532
Whang, C.N., see Cho, S.J. . . . B59/60 (1991) 1245
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White, C.W., see Holland, O.W. . . . B59/60 (1991) 353
White, C.W., see Golanski, A. . . . B59/60 (1991) 444
White, C.W., see Xia, W. . . . B59/60 (1991) 491
White, C.W., see Vallet, C.E. . . . B59/60 (1991) 855
White, C.W., see Sklad, P.S. . . . B59/60 (1991) 1187
White, R.C., see Jeong, H.-S. . . . B59/60 (1991) 1285
Whitton, J.L., see Laursen, T. . . . B59/60 (1991) 768
Whitton, J.L., see Clapham, L. . . . B59/60 (1991) 1404
Wiedersich, H., The effect of defect clusters formed in cascades on the sink strength of irradiated materials . . . B59/60 (1991) 51
Wilbur, P.J., see Wei, R. . . . B59/60 (1991) 731
Wilbur, P.J., see Williamson, D.L. . . . B59/60 (1991) 737
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Williamson, D.L., see Wei, R. . . . B59/60 (1991) 731
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Wing, R.G., see Nielsen, B.R. . . . B59/60 (1991) 772
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Wolf, G.K., see Barth, M. . . . B59/60 (1991) 254
Wolf, G.K., see Liu Xianghuai . . . B59/60 (1991) 851
Woo, J.J., L. Funk, P.M. Baldo and L.E. Rehn, Elevated-temperature implantations of Au into Zr . . . B59/60 (1991) 537
Woo, J.J., see Kim, H.K. . . . B59/60 (1991) 554
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Woolcott, R., see Soble II, C.N. . . . B59/60 (1991) 155
Worzala, F.J., see Qiu, X. . . . B59/60 (1991) 951
Wu, M.F., see Vantomme, A. . . . B59/60 (1991) 680
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Wu, R.L.C., see Bhattacharya, R.S. . . . B59/60 (1991) 1383
Wu, X.-G., see Li, J.-C. . . . B59/60 (1991) 1110
Wu, X.H., see Zhu, J.L. . . . B59/60 (1991) 1045
Wu Yuejin, see Yu Zengliang . . . B59/60 (1991) 705
Wu Yuguang, see Zhang Tonghe . . . B59/60 (1991) 1098

Xi, W., see Hagmann, D.R. . . . B59/60 (1991) 110
Xi, X.X., see Linker, G. . . . B59/60 (1991) 1458
Xia, B.-H., see Li, J.-C. . . . B59/60 (1991) 1110
Xia, G.Q., see Xu, X.L. . . . B59/60 (1991) 1267
Xia, W., S.N. Hsu, C.C. Han, S.A. Pappert, B. Zhu, C. Cozzolino, P.K.L. Yu, S.S. Lau, D.B. Poker, C.W. White and S.A. Schwarz, Ion mixing of semiconductor superlattices . . . B59/60 (1991) 491
Xia, W., see Li, J. . . . B59/60 (1991) 989
Xiao, Y.-W., see Li, J.-C. . . . B59/60 (1991) 1110
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Yabe, K., see Matthews, A.P. . . . B59/60 (1991) 671
Yabe, K., see Fukui, Y. . . . B59/60 (1991) 812
Yabumoto, H., see Koshida, N. . . . B59/60 (1991) 1236

Yacout, A.M., N.Q. Lam and J.F. Stubbins, Dynamical behavior of the implant profile during ion implantation at elevated temperatures . . . B59/60 (1991) 57
Yacout, A.M., see Lam, N.Q. . . . B59/60 (1991) 889
Yamada, A., see Yamada, I. . . . B59/60 (1991) 219
Yamada, A., see Zuhr, R.A. . . . B59/60 (1991) 308
Yamada, I., see Brown, W.L. . . . B59/60 (1991) 182
Yamada, I., see Hirayama, H. . . . B59/60 (1991) 207
Yamada, I., G.H. Takaoka, H. Usui, F. Satoh, Y. Itoh, K. Yamashita, S. Kitamoto, Y. Namba, Y. Hashimoto, Y. Maeyama and K. Machida, X-ray characteristics of atomically flat gold films deposited by ICB . . . B59/60 (1991) 216
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Yamada, I., see Zuhr, R.A. . . . B59/60 (1991) 308
Yamada, I., see Ito, K. . . . B59/60 (1991) 321
Yamada, I., Advanced ion beam processing projects in Japan . . . B59/60 (1991) 1467
Yamada, I., see Adachi, M. . . . B59/60 (1991) 940
Yamada, K., see Adachi, M. . . . B59/60 (1991) 940
Yamaguchi, S., see Takahiro, K. . . . B59/60 (1991) 1374
Yamanishi, K., see Kawagoe, Y. . . . B59/60 (1991) 1426
Yamasaki, T., see Takahiro, K. . . . B59/60 (1991) 9
Yamasaki, T., see Takahiro, K. . . . B59/60 (1991) 1374
Yamashita, K., see Yamada, I. . . . B59/60 (1991) 216
Yamashita, K., see Oyoshi, K. . . . B59/60 (1991) 1324
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Yang, F.J., see Lin, S.H. . . . B59/60 (1991) 1257
Yang, L., see Becker, K. . . . B59/60 (1991) 1304
Yang, Y.Z., see Pan, X.Z. . . . B59/60 (1991) 233
Yang Genqing, see Wang Xi . . . B59/60 (1991) 272
Yang Genqing, see Chen Yuanru . . . B59/60 (1991) 1295
Yang Jianhua, see Zhang Tonghe . . . B59/60 (1991) 828
Yano, S., see Nakane, Y. . . . B59/60 (1991) 264
Yasuda, K., see Nishi, Y. . . . B59/60 (1991) 1422
Ye, M., E.P. Burte and H. Ryssel, Formation of cobalt silicide by ion beam mixing . . . B59/60 (1991) 528
Yedave, S.N., see Viswanathan, R. . . . B59/60 (1991) 1439
Yelon, A., see Touhouche, K. . . . B59/60 (1991) 676
Yoko-o, H., see Miyano, T. . . . B59/60 (1991) 1167
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Yonemitsu, T., see Ito, K. . . . B59/60 (1991) 321
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Yu, P.K.L., see Xia, W. . . . B59/60 (1991) 491
Yu, T., see Pan, X.Z. . . . B59/60 (1991) 233
Yu, Y.H., see Xu, X.L. . . . B59/60 (1991) 1267
Yu, Z.W., see Zhu, J.L. . . . B59/60 (1991) 1045
Yust, C.S., see Rai, A.K. . . . B59/60 (1991) 280
Yust, C.S., see Bhattacharya, R.S. . . . B59/60 (1991) 1383
Yu Zengliang, Deng Jianguo, He Jianjun, Huo Yuping, Wu Yuejin, Wang Xuedong and Lui Guifu, Mutation breeding by ion implantation . . . B59/60 (1991) 705

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Zhang, B.-X., see Wang, Z.-L. . . . B59/60 (1991) 439
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Zhang, L., see Chandler, P.J. . . . B59/60 (1991) 1223
Zhang, P.J., see Zhang, B.-X. . . . B59/60 (1991) 434

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Zhang Tonghe, Zhou Shenghui, Wu Yuguang, Luo Yan and Zhou Zuyao, The influence of high dose and elevated-temperature implantation on pn-junction leakage current during rapid thermal annealing B59/60 (1991) 1098
Zhang Xushou, see Chen Yuanru B59/60 (1991) 1295
Zheng, J.G., see Zhang, B.-X. B59/60 (1991) 434
Zheng, L.R., see Braunstein, G. B59/60 (1991) 1032
Zheng Zhihong, see Wang Xi B59/60 (1991) 272
Zhou, W. and D.K. Sood, Blistering and exfoliation during annealing of *a*-axis oriented α-Al_2O_3 single crystals implanted with oxygen ions B59/60 (1991) 1195
Zhou, Z.Y., see Zhang, S.K. B59/60 (1991) 690
Zhou, Z.Y., see Zhang, T.Q. B59/60 (1991) 1007
Zhou, Z.Y., see Zhu, J.L. B59/60 (1991) 1045
Zhou, Z.Y., see Lin, S.H. B59/60 (1991) 1257
Zhou, Z.Y., see Xu, X.L. B59/60 (1991) 1267
Zhou Shenghui, see Zhang Tonghe B59/60 (1991) 1098
Zhou Zuyao, see Wang Xi B59/60 (1991) 272
Zhou Zuyao, see Li Jinhua B59/60 (1991) 685
Zhou Zuyao, see Tan Hui B59/60 (1991) 785
Zhou Zuyao, see Zhang Tonghe B59/60 (1991) 1098
Zhu, B., see Xia, W. B59/60 (1991) 491
Zhu, B., see Li, J. B59/60 (1991) 989
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Zhu, X.F., see Lin, S.H. B59/60 (1991) 1257
Zhu, Z.L., see Pan, X.Z. B59/60 (1991) 233
Ziemann, P., see Miehle, W. B59/60 (1991) 410
Zocco, T.G., see Nastasi, M. B59/60 (1991) 806
Zou, S.C., see Zhang, S.K. B59/60 (1991) 690
Zou, S.C., see Xu, X.L. B59/60 (1991) 1267
Zou Shichang , see Wang Xi B59/60 (1991) 272
Zou Shichang, see Li Jinhua B59/60 (1991) 685
Zou Shichang, see Liu Xianghuai B59/60 (1991) 851
Zuev, A.P., see Vyatkin, A.F. B59/60 (1991) 431
Zuhr, R.A., T.E. Haynes, M.D. Galloway, S. Tanaka, A. Yamada and I. Yamada, Formation of aluminum films on silicon by ion beam deposition: a comparison with ionized cluster beam deposition B59/60 (1991) 308
Zuhr, R.A., see Becker, K. B59/60 (1991) 1304
Zuhr, R.A., see Magruder III, R.H. B59/60 (1991) 1308